

—第二届中国互连技术与产业大会

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# 基于ADC/DSP的高速串行接口物理 层的研究方法与关键技术

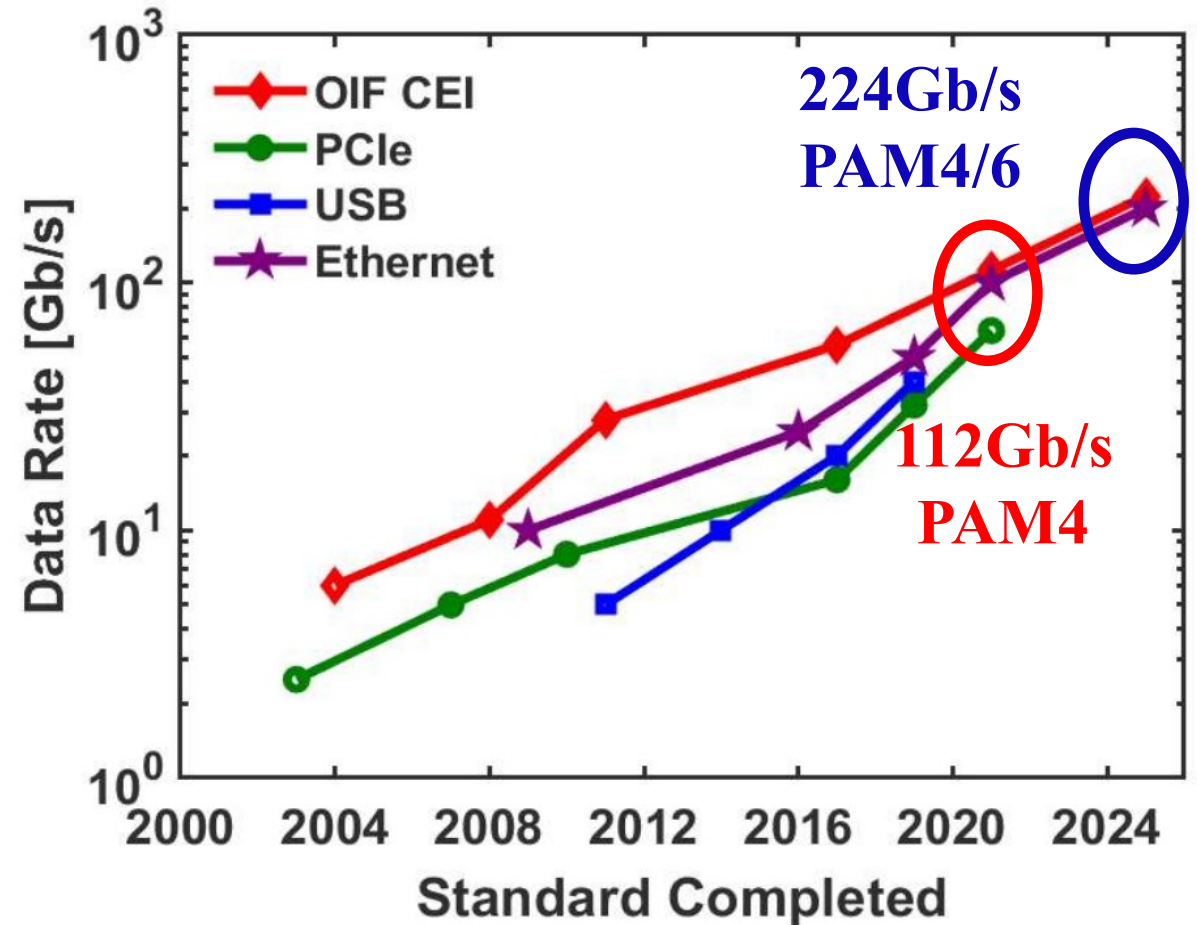
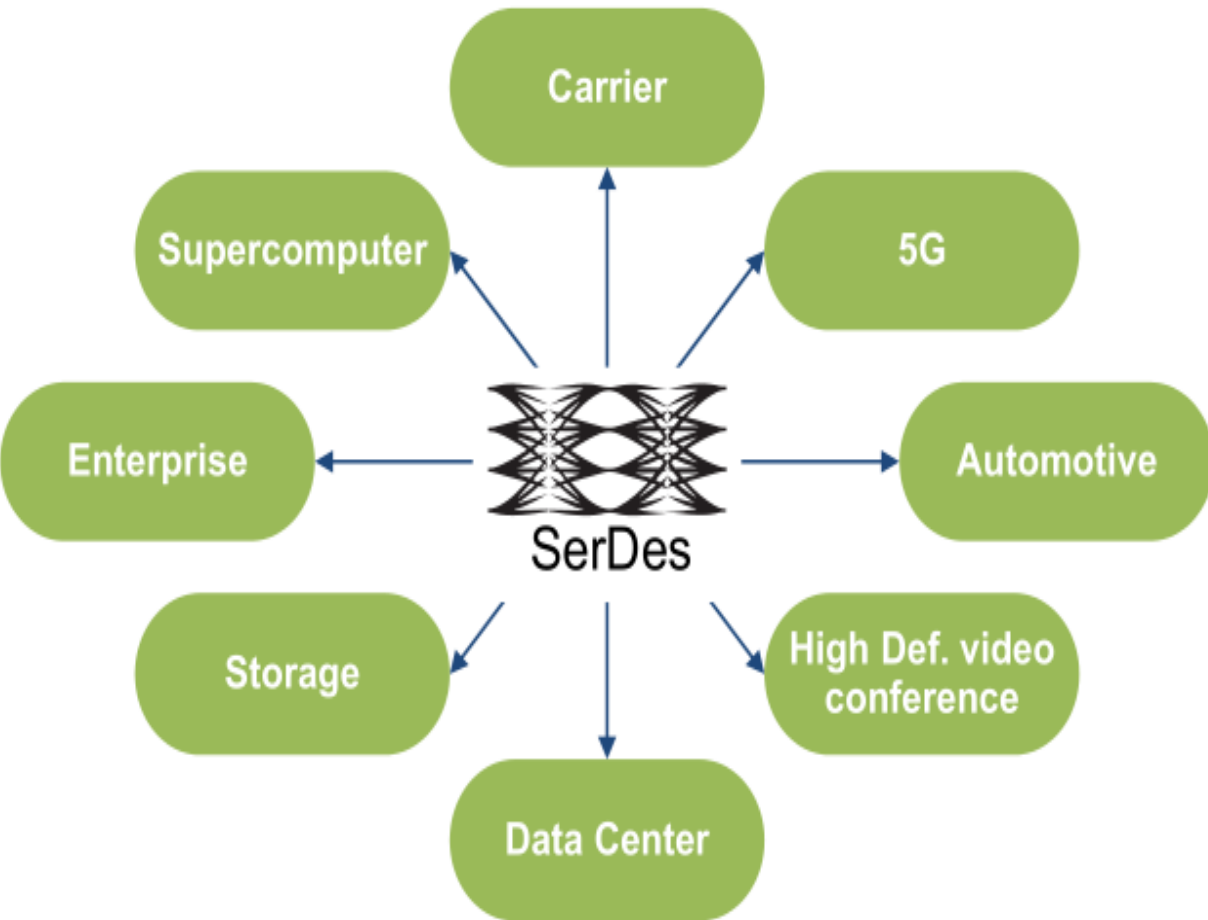
郑旭强

中国科学院微电子研究所

2022 .12 .16

- SerDes发展趋势与应用场景
- SerDes研究方法与关键技术
  - ◆ 系统级建模与仿真
  - ◆ 电路级技术演进
- 基于ADC/DSP PAM4 收发机

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T. Musah, "Wireline Link Standard," [Online]. Available: <https://mics.engineering.osu.edu/iostandards>

**Per-lane data rate has doubled every 3-4 years.**

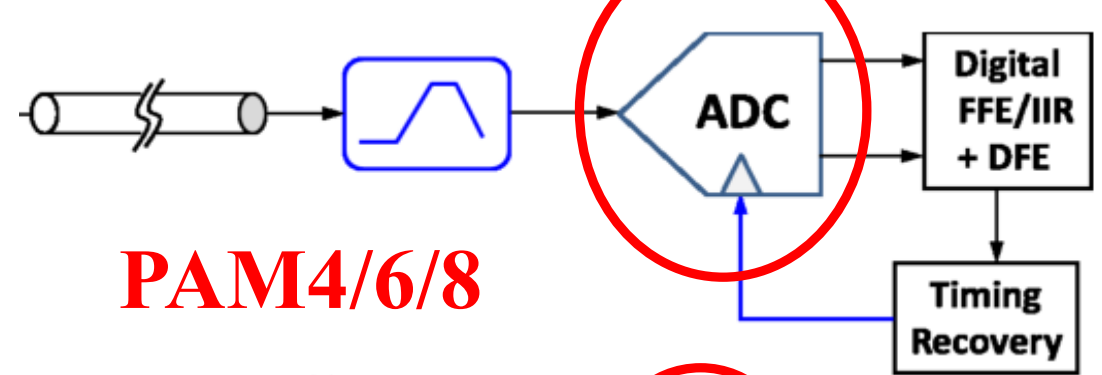
# 当前112Gb/s-SerDes-ADC+DSP已成为主流

* Process	DR (Gb/s)	TYPE	TX			RX	POWER EFFE.	LOSS (dB)	REFERENCE
			EQ	DRV	AEQ	STRUCTURE			
1 5nm	224 PAM-4	RX	-	-	CTLE/VGA	6BI TADC+DSP	1.41	31.6	Intel, ISSCC 2022
5 10nm	224 PAM-4	TX	8 FIR	DAC-CML	-	-	2.25	-	Intel, ISSCC 2021
2 5nm	112 PAM-4	TRX	6 FIR	DAC-SST	CTLE/VGA	7BIT ADC+30 FFE/1 DFE	4.5	40	Marvell, ISSCC 2022
3 7nm	60 PAM-4	TRX	7 FIR	DAC-SST	CTLE/VGA	14 DFE	3.03	47.5	Broadcom, ISSCC 2022
7 7nm	112 PAM-4	TRX	3-7 FIR	DAC-SST/CML	CTLE/VGA	7BIT ADC+25 FFE/2 DFE	5.9	45-52	Huawei, ISSCC 2021
8 7nm	112 PAM-4	TRX	4 FIR	DAC-CML	CTLE/VGA	ADC+DSP	6.51	>40	Inphi, ISSCC 2021
9 7nm	112 PAM-4	TRX	8 FIR	DAC-SST	CTLE/PGA	7 BIT ADC+32 FFE/1 DFE	8.2	26	eTopus Technology, ISSCC 2021
10 7nm	112 PAM-4	TRX	6 FIR	DAC-SST	CTLE/VGA	7BIT ADC+8-24 FFE/1 DFE	4.29	38.9	MediaTek, ISSCC 2020
11 7nm	112 PAM-4	TRX	4 FFE	CML	CTLE/PGA	7 BIT ADC+31 FFE/1 DFE	5.38	37.5	Xilinx, ISSCC 2020
12 7nm	10-112 PAM-4	TX	7 FIR	DAC-SST	-	-	1.56	-	Rambus, ISSCC 2020
13 14nm	100 PAM-4	RX	-	-	CTLE/VGA	8 FFE/1 DFE	1.1	20	IBM, ISSCC 2019
14 14nm	128 PAM-4	TX	3 FFE	CML	-	-	1.3	-	IBM, ISSCC 2019
15 40nm	112 PAM-4	TX	4 FFE	SST	-	-	3.89	5.5	Teletrx, ISSCC 2019
16 10nm	112 PAM-4	TX	3 FFE	CML	-	-	2.07	31	Intel, ISSCC 2018
17 14nm	112 PAM-4	TX	8 FFE	DAC-SST	-	-	2.6	-	IBM, ISSCC 2018
18 16nm	19-56 PAM-4	TRX	4 FIR	SST	CTLE/VGA	7 BIT ADC+14 FFE/1 DFE	9.7	32	Xilinx, ISSCC 2018
19 16nm	64 PAM-4	TRX	3 FFE	SST	CTLE/VGA	1+5BIT ADC+FFE/ DFE	5.84	29.5	University of Toronto, ISSCC 2018

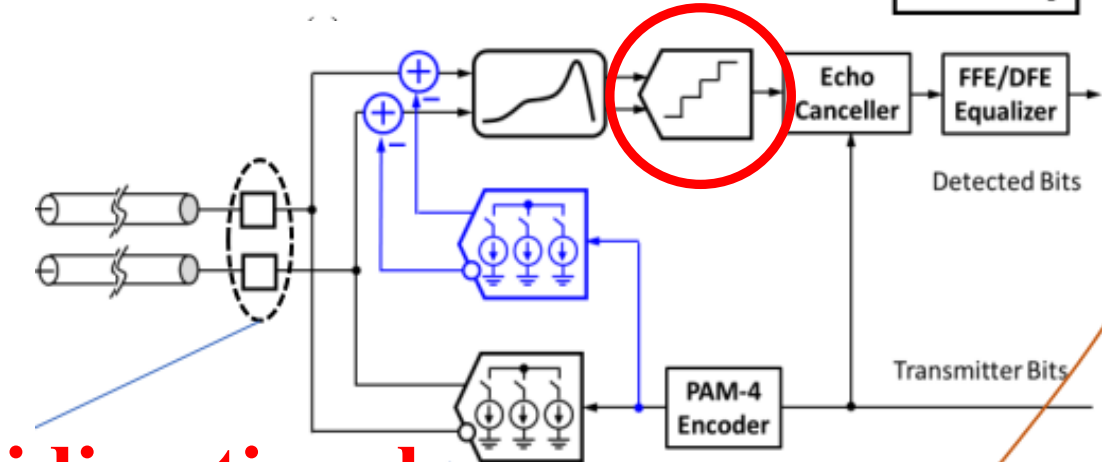


# 下一代224Gb/s实现方案-ADC+DSP构架主导

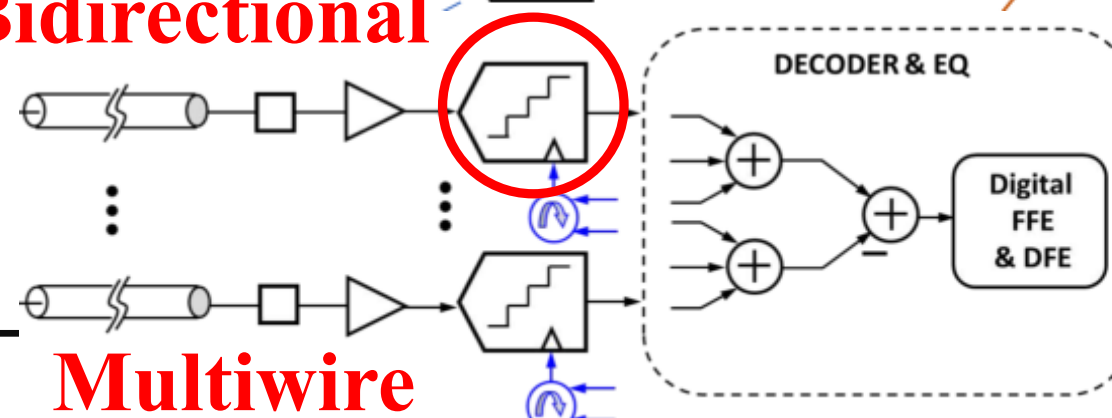
		PAM-4 112 Gb/s	PAM-4 224 Gb/s	PAM-8 224 Gb/s	Multiwire Encoding 224 Gb/s	Bidirectional Signalling 224 Gb/s
Nyquist Frequency		28 GHz	56 GHz	39 GHz	67 GHz	28 GHz
channel	XSR-USR	$<10^{-6}$	$<10^{-6}$	$<10^{-3}$	$<10^{-8}$	$<10^{-5}$
	MCM	$<10^{-6}$	$<10^{-4}$	$>10^{-2}$	$<10^{-6}$	$<10^{-4}$
	Chip-to-module	$<10^{-6}$	$>10^{-2}$	$>10^{-2}$	$<10^{-4}$ (<45 dB) $>10^{-2}$ (>45 dB)	$<10^{-4}$
ADC Resolution		6 bit	6 bit	8 bit	5 bit	8 bit
ADC Power		1x	3x	2.8x	2.5x	3x
Equalizer		10 tap FFE & 1 tap DFE	10 tap FFE & 1 tap DFE	10 tap FFE & 1 tap DFE	8 tap FFE & 3 tap DFE	10 tap FFE & 1 tap DFE & 5-tap Echo-Canceller
Jitter Requirement		150 fs	80 fs	130 fs	125 fs	130 fs
Power		1x	2.8x	2.5 x	2.5 x	3x



**PAM4/6/8**



**Bidirectional**



**Multiwire**

下一代224Gb/s的备选实现方案均基于ADC+DSP构架

Ref: 2021-TCPM-Toward 224-Gb/s Electrical Signaling—Modulation, Equalization, and Channel Options

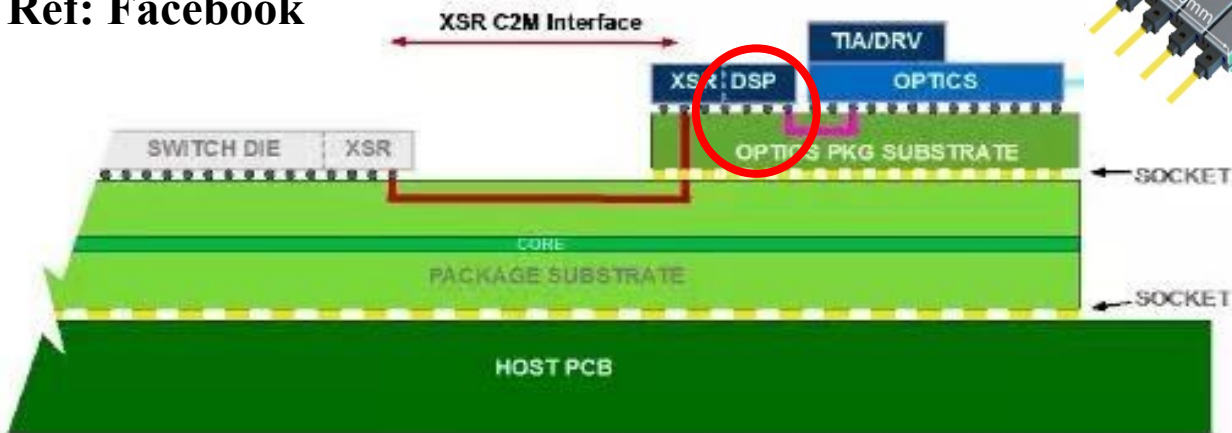




# CPO-DSP依然不可或缺

## Gen 1: 112G XSR AUI

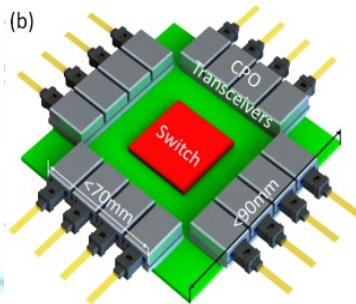
Ref: Facebook



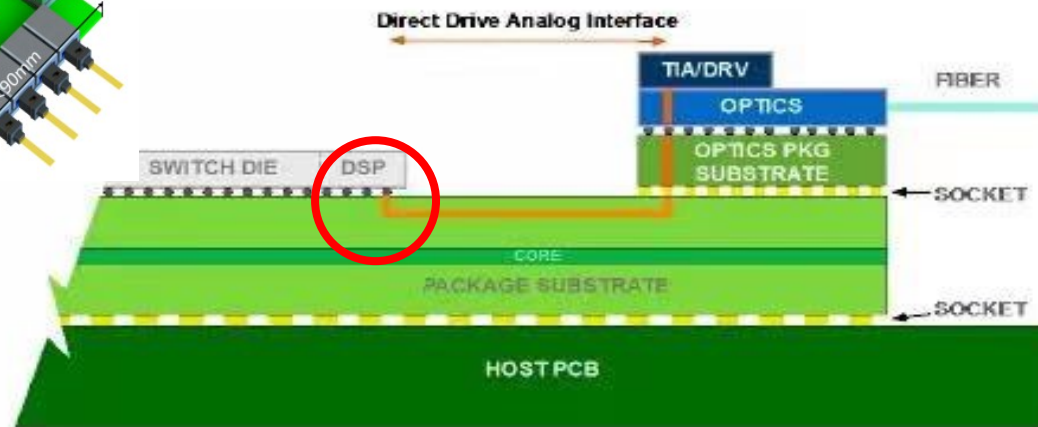
- Switch Generation: 51.2T
- Lane Speed: 106 Gb/s
- Interface Architecture: XSR based AUI, 400G-FR4 PMD (& 200G-FR4 down-speed)
- Motivation: System Power Reduction, Ecosystem & Operational Readiness

**Target: Lower Power**

**Method: Short Connection Distance**



## Gen 2: "Direct Drive"



- Switch Generation: 102.4T
- Lane Speed: 212 Gb/s (?)
- Interface Architecture: Direct-Drive to Optics (analog) 800GBASE-FR4 compatible (& 400G-FR4)

*[Requires new standardization work on direct drive. note: will not support BiDi, or lane gearboxing]*

- Motivation: System Power Reduction & Bandwidth Scaling (Densification)



Facebook - OIF CPO Webinar 2020

**DSP: Optical Loss, dispersion, nonlinearity...**

# 400G-ZR 相干光通信-ADC+DSP核心芯片

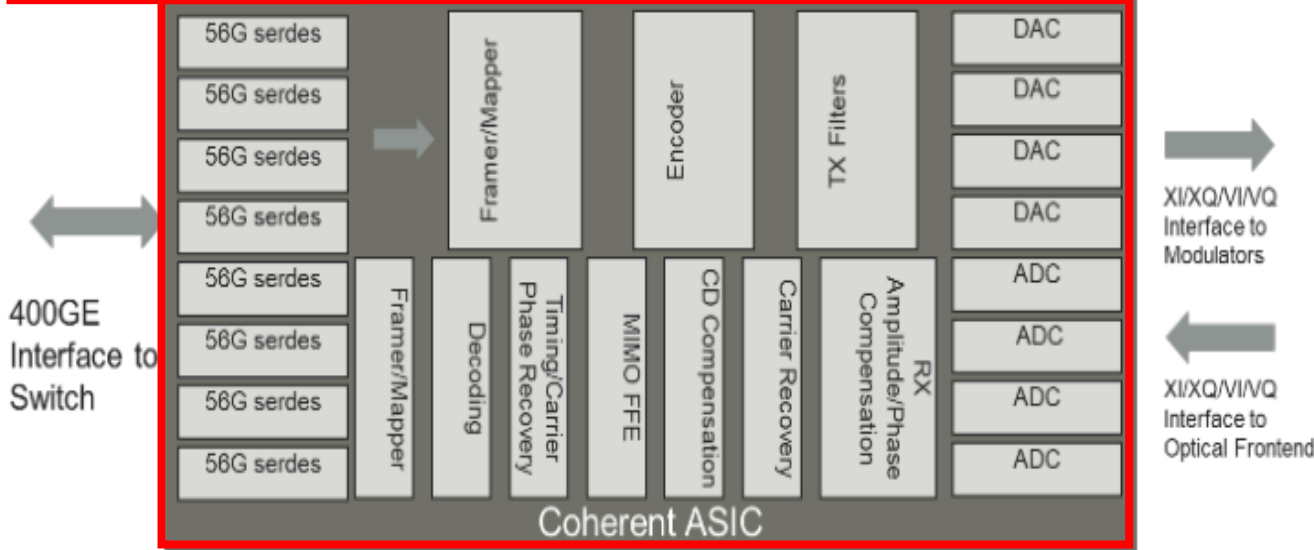
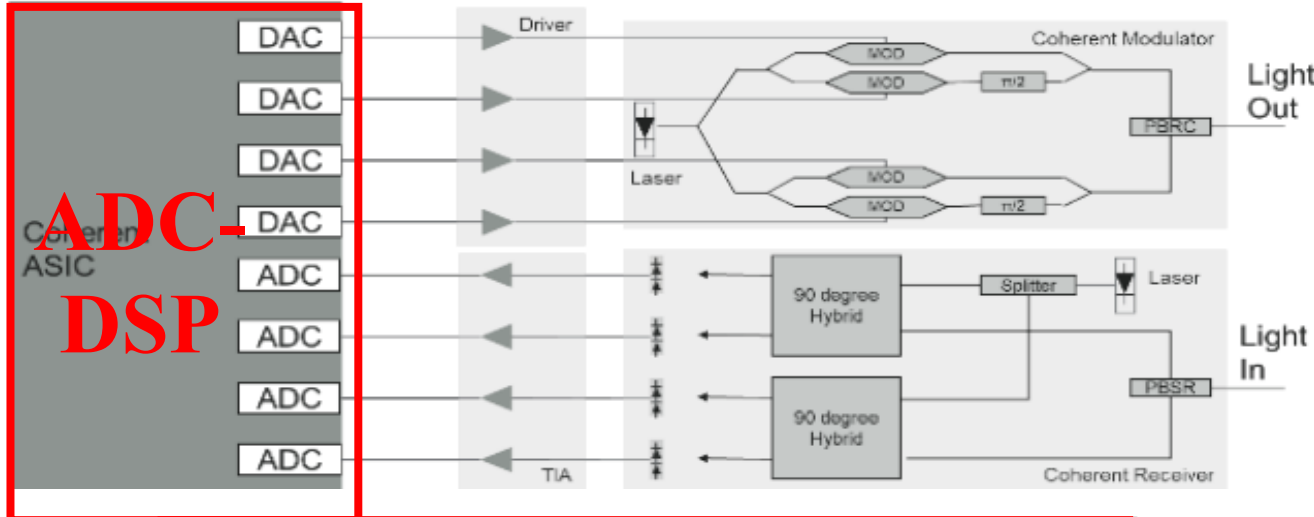


Table 1: Definition of an ASIC for 400ZR

Type of line interface	400ZR
Symbol rate of line interface	59.87GHz
Number of electrical lanes	4
Modulation of line interface	DP-QAM16
FEC of line interface	C-FEC with 15% overhead
Pilot overhead of line interface	3%
ROSNR Tolerance	26db
Chromatic Dispersion Tolerance	2400ps/nm
Type of Host interface	400GAUI-8
Number of host lanes	8
Symbol rate of host interface	26.5625GHz
Modulation of host interface	PAM4
FEC of host interface	RS(544,514)
Link Loss Budget	10.2db

**Bandwidth: 40GHz**

**Sample rates: 97Gsamples/s**

**Resolution: 8bit**

**Jitter: 150fsrms**

**Energy Efficiency: 35fJ/conversion-step**

**ASIC Energy Efficiency: 40-60pJ/bit**

Ref: OFC-2022-Marvell-Development of Low-power Coherent ASIC



# 2.5D/3D 短距相干光通信-ADC+DSP变化不大

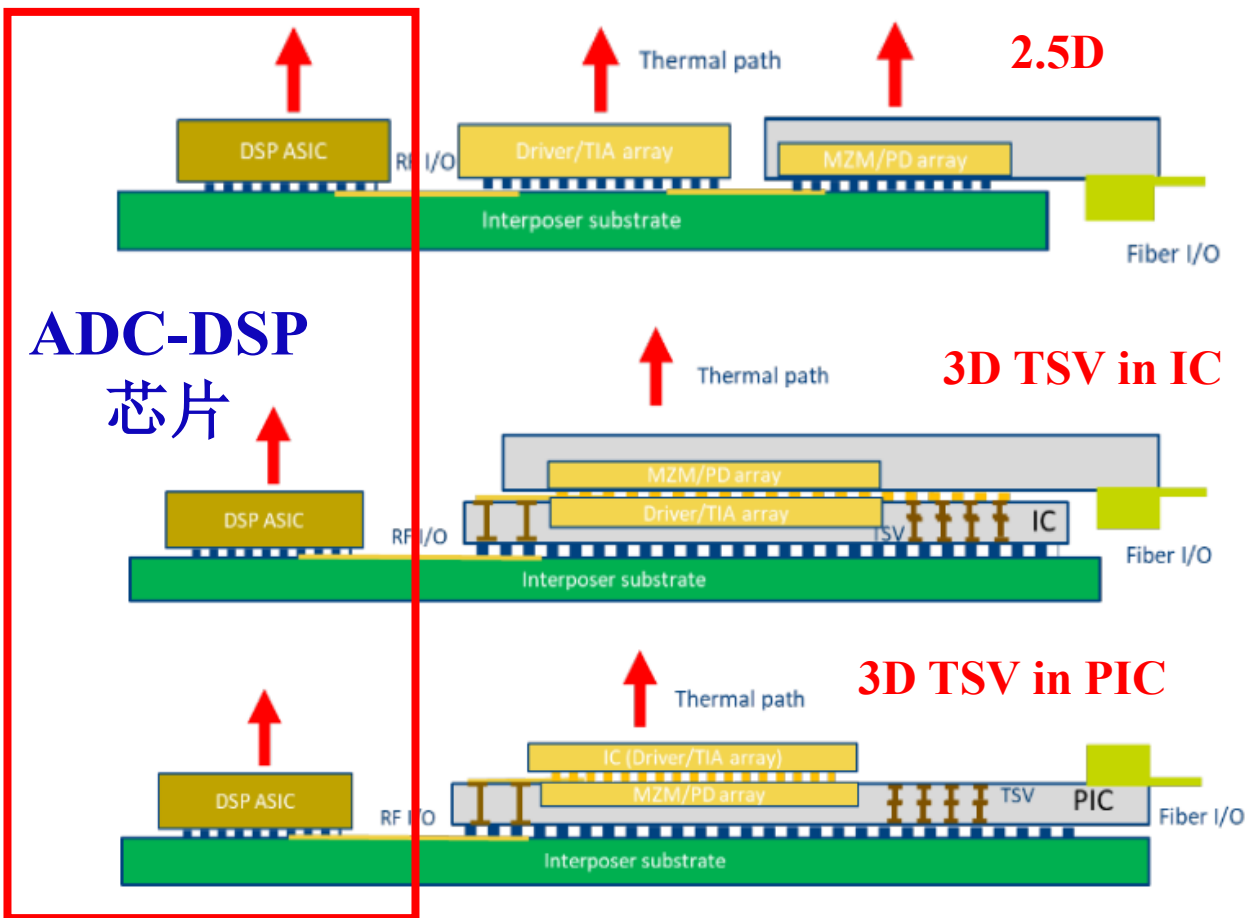


Fig. 5. 2.5D/3D silicon photonic-electronic integration with PIC, IC and DSP, and optical I/O and RF I/O for coherent transceiver without TSV in IC and PIC as 2.5D (upper), TSV in IC as 3D (middle), and TSV in PIC (lower).

Table 8 Power budget for 6.4T/s coherent transceiver

	Power, W	Efficiency, pJ/bit
<b>Integrated IC/PIC</b>		
PIC	2.5	0.4
Driver	16.3	2.6
TIA	12.8	2.0
Integrated IC/PIC	31.6	4.9
<b>DFB lasers</b>		
4 LO Lasers	4.4	0.7
4 Tx lasers	5.8	0.9
Total 8x DFB Lasers	10.3	1.6
<b>Transceiver optics (IC/PIC + lasers)</b>		
Transceiver optics	41.9	6.5
<b>DSP ASIC predicted</b>		
DSP ASIC, predicted	32.0	5.0
<b>Transceiver</b>		
Misc, predicted	2.0	0.3
Transceiver, predicted	75.9	11.9

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# 高速串行接口通信核心问题

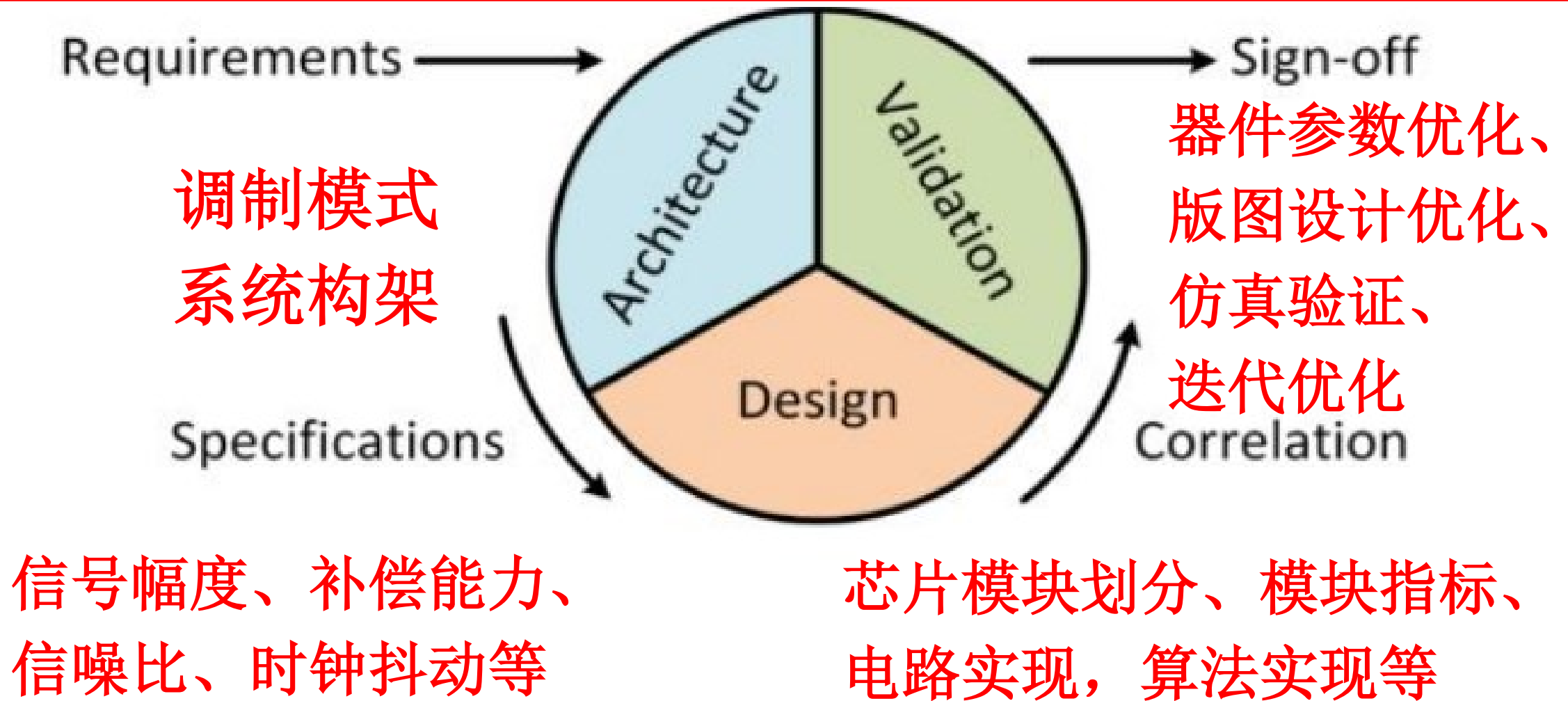
高速串行接口演进驱动力：用尽量低的**功耗、面积及链路成本**解决好尽量**高速率**下的**横向时序和纵向信噪比**的信号完整性问题。

◆ **纵向信噪比**：数据均衡设计---**Data Path**

◆ **横向时序**：时钟定时设计---**Clock Path**

◆ **高速率**：宽带扩展设计

# 高速SerDes的设计阶段



Ref: 2022-DesignCon-Aleksey Tyshchenko, et. al-Parametric System Model of a 112Gbps ADC-based SerDes for Architectural, Design & Validation Project Phases

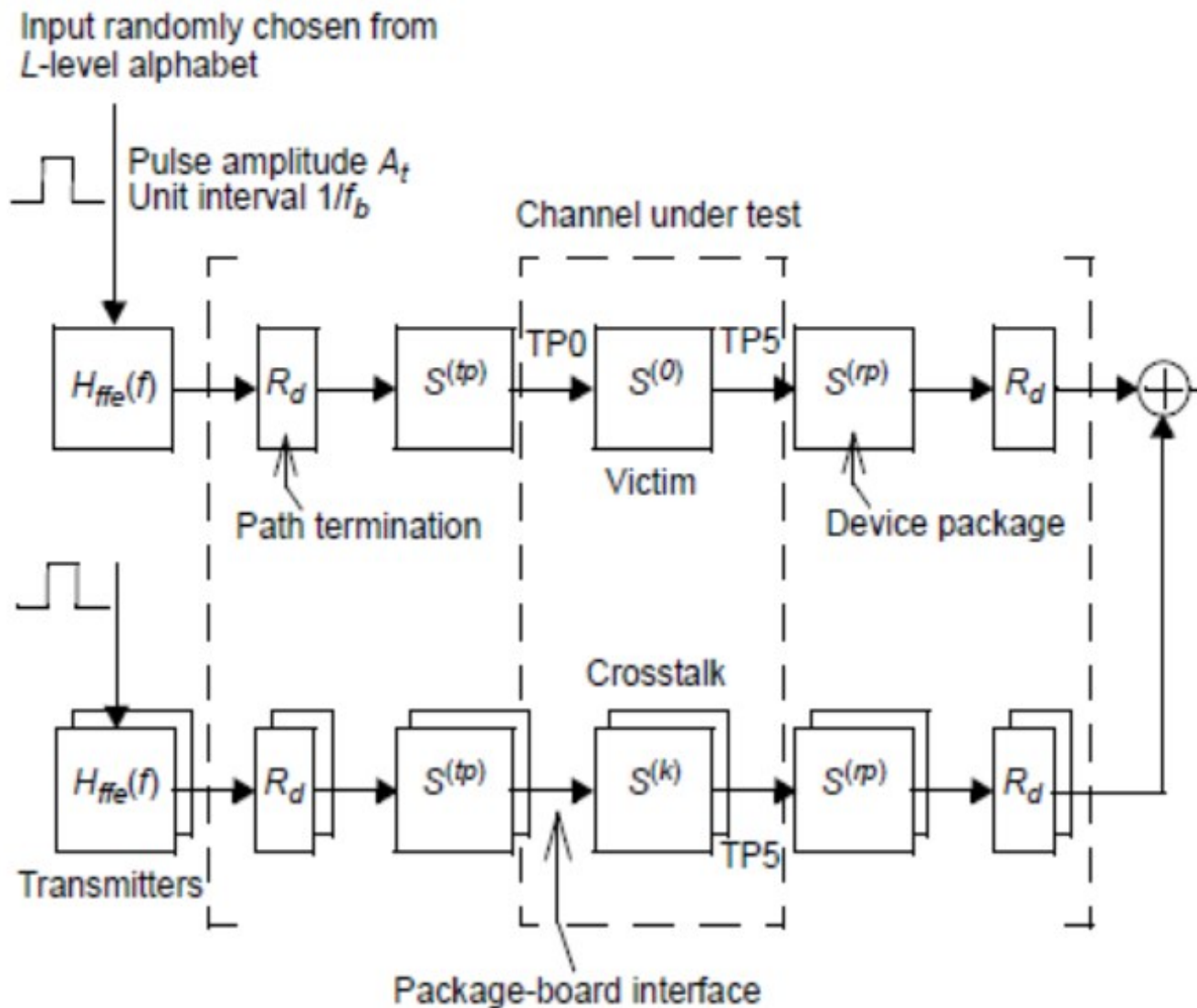
## 基于SerDes电气约束验证实际 信道对通信标准的满足情况

### 特点

- ◆ LTI线性时不变系统
- ◆ 纵向幅度统计特性分析

### 挑战

- ◆ 非线性问题
- ◆ 横向抖动特性分析
- ◆ 精度问题



COM Reference Model



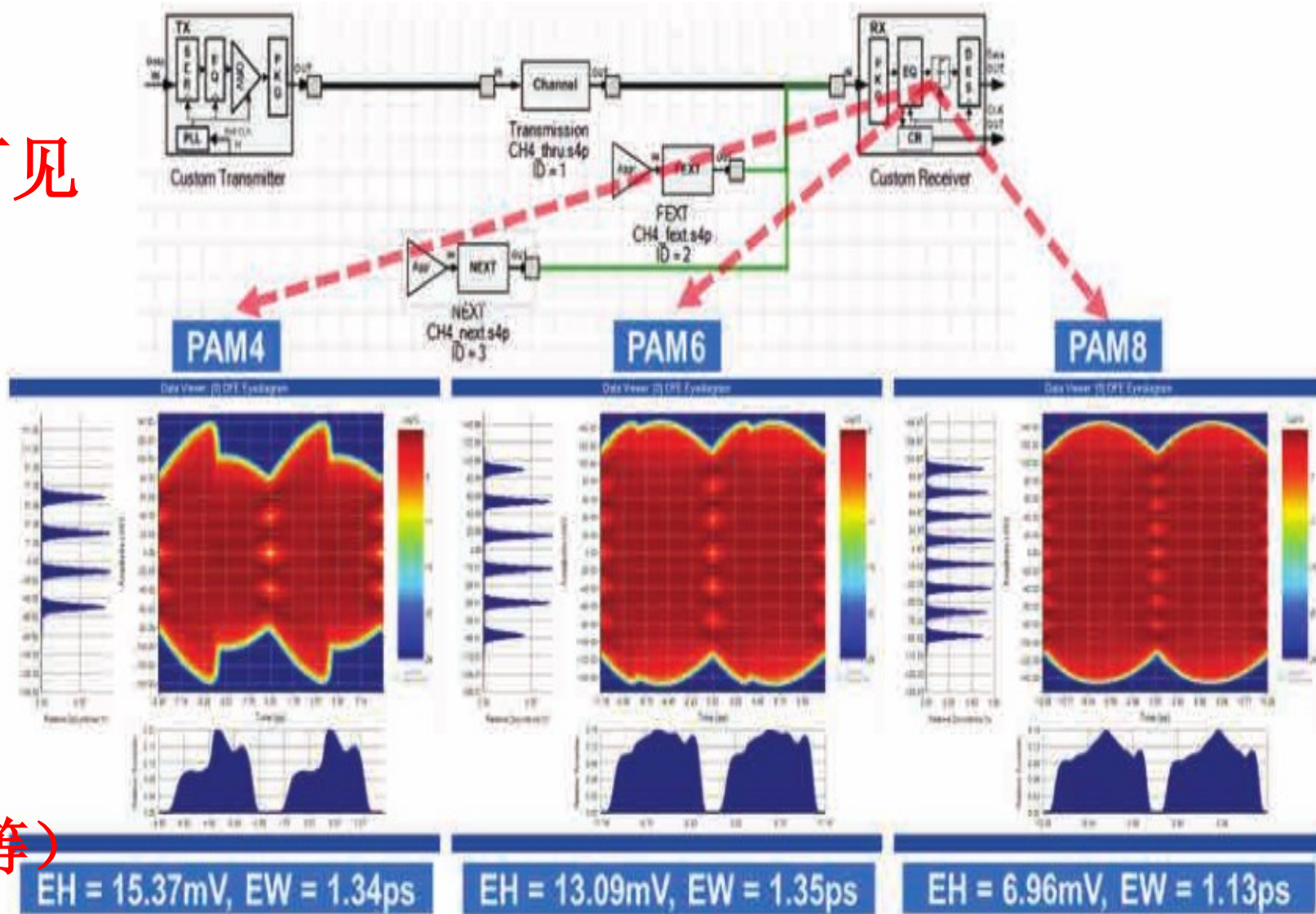
# System-Level-Simulation-时域bit-by-bit链路仿真 14/36

## 优势

- ◆ 时域模型-波形直观可见
- ◆ 模型可分析纵向噪声
- ◆ 模型可分析横向抖动

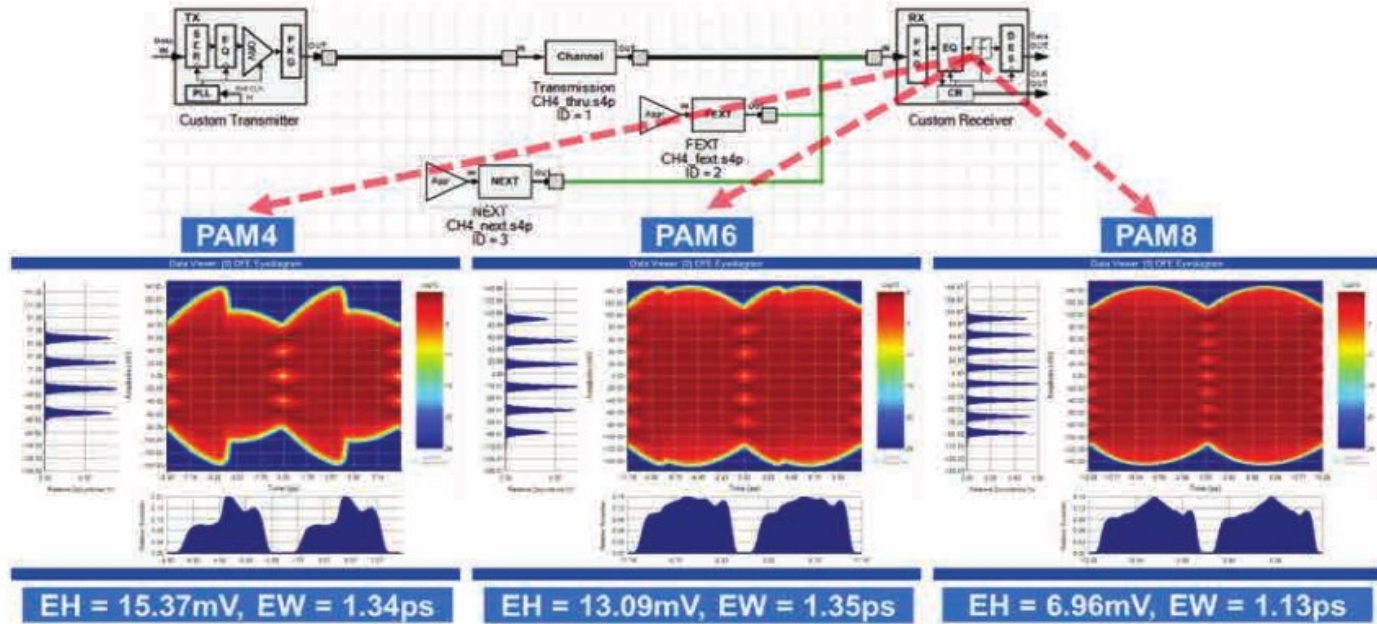
## 挑战-精度问题

- ◆ 噪声精度
- ◆ 抖动精度
- ◆ 模拟电路特性
- ◆ 工作环境（PVT，供电等）





# System-Level-Simulation-时域bit-by-bit链路仿真 15/36



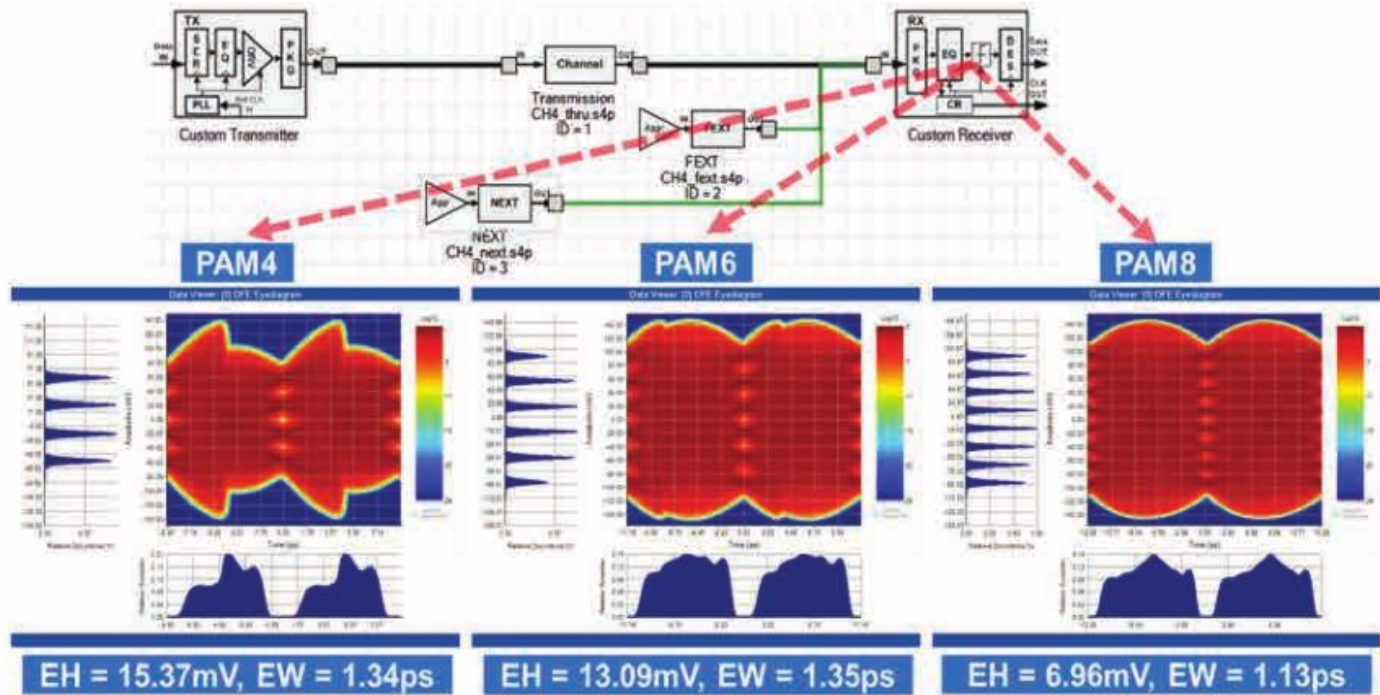
Ref 2022-SI-224 Gb/s Modulation and Channel Characteristics

- ◆ 研究积累：系统构架/均衡方案/抖动分配等
- ◆ 原型芯片测试数据：转换沿/关键模块特性
- ◆ 封装测试数据：信道衰减串扰；
- ◆ 原理性分析：输出噪声/输入参考噪声；
- ◆ 编程与分析能力等

## Simulation Configuration:

- Data Rate: 224 Gb/s **研究积累与设计基础**
  - Modulation Scheme: PAM4, PAM6, PAM8
  - Test Pattern: PRBS-31 with PAM4/PAM6/PAM8 coding
- Transmitter Configuration:
- 20 to 80 percent Rise/Fall Time: Correlated to Intel 224 Gb/s test chip<sup>1</sup>
  - AFE Characteristics: Correlated to Intel 224 Gbps test chip<sup>1</sup>
  - TX EQ: 4 pre-taps and 1 post-tap
  - Separation Level Mismatch (RLM): 0.95
  - Jitter: duty-cycle distortion (DCD): 0.019 UI<sub>peak-peak</sub>, bounded uncorrelated jitter (BUJ): 0.04 UI<sub>peak-peak</sub>, random jitter (RJ): 0.01 UI<sub>RMS</sub>
  - Noise: 11.19 mVRMS (corresponding to transmitter output SNR of 33 dB)
  - Package: 31 mm, per Intel package 2024-2025 projection
- Receiver Configuration:
- AFE Characteristics: Correlated to Intel 224 Gbps test chip<sup>1</sup>
  - RX EQ: continuous time linear equalization and RX FFE+DFE: three pre-tap, 24 post-tap, floating taps with six banks of three consecutive taps up to 80 taps
  - RX Jitter/Noise: RX input referred noise:  $4.1 \times 10^{-9} \text{ V}^2/\text{GHz}$
  - Package: 29 mm, per Intel package 2024-2025 projection. The channel characteristics of all test channels is shown in

# System-Level-Simulation-时域bit-by-bit链路仿真 16/36



- ① 新调制模式探索与传输信道需求
  - ◆ 不同调制模式比较
  - ◆ 不同信道的效果比较

## ② 系统级指标分频

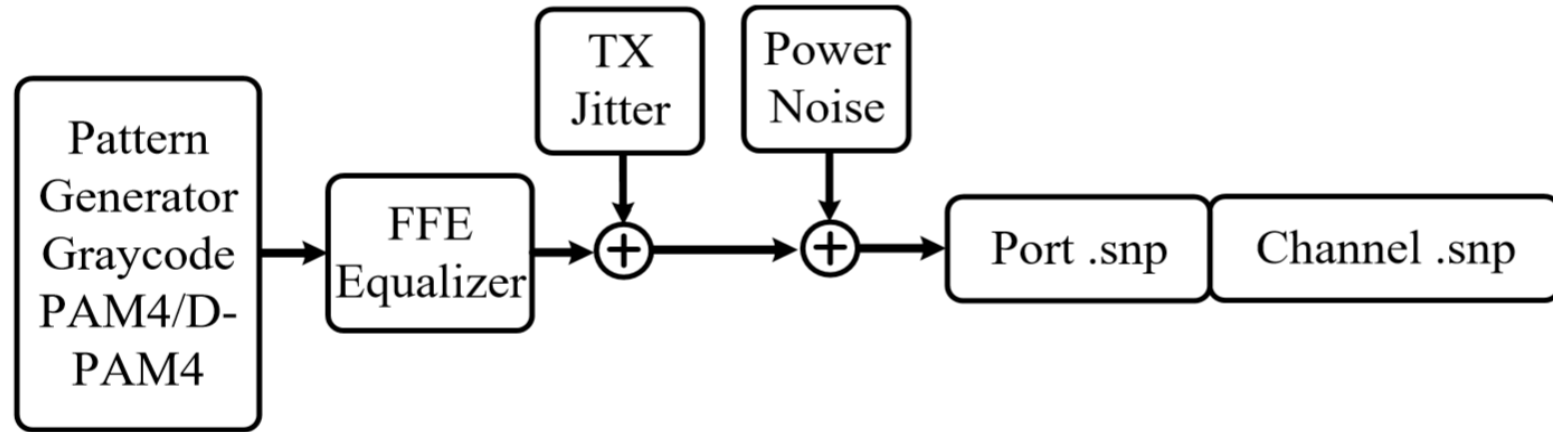
- ◆ 信号幅度、
- ◆ 补偿能力、
- ◆ 信噪比、
- ◆ 时钟抖动等

## ③ DSP算法验证

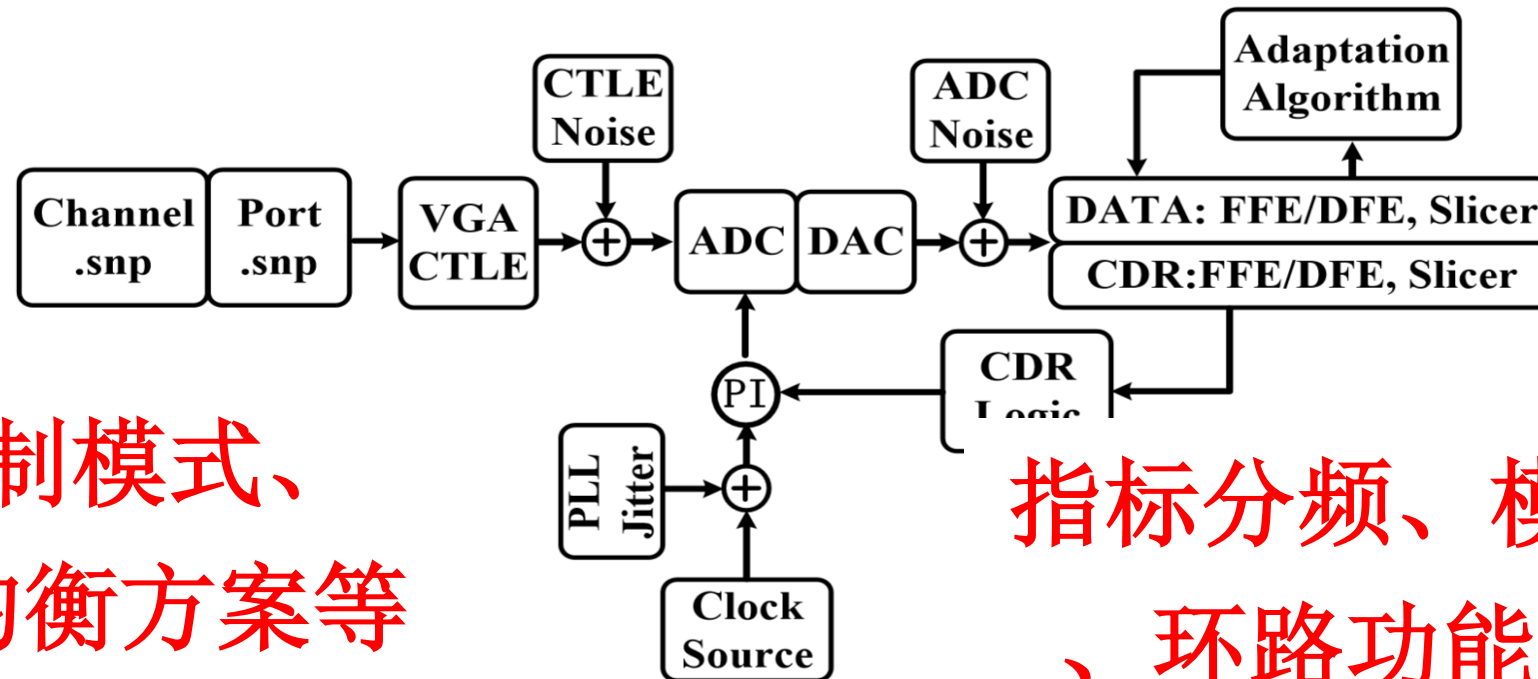
- ◆ ADC校准算法
- ◆ FFE/DFE实现
- ◆ CDR设计实现
- ◆ 自适应算法

Ref 2022-SI-224 Gb/s Modulation and Channel Characteristics

## 发送端模型



## 接收端模型

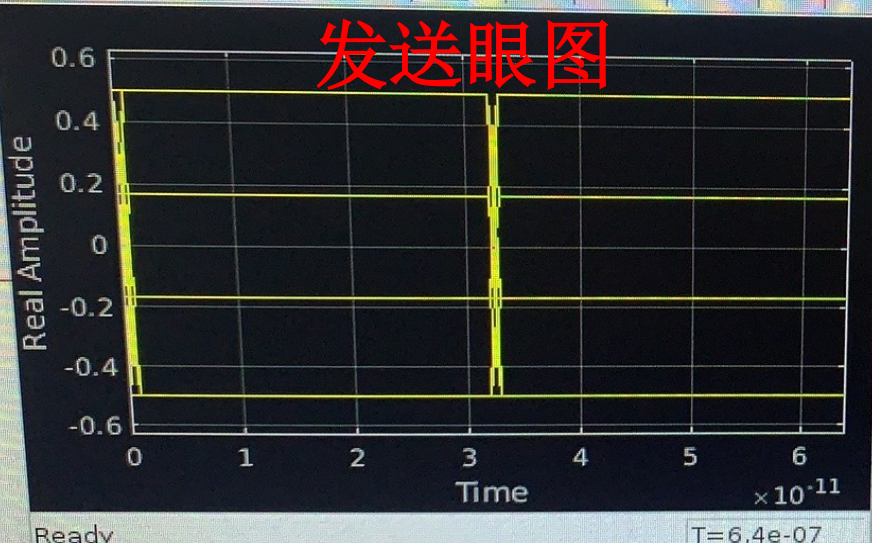


探索新的调制模式、  
系统构架、均衡方案等

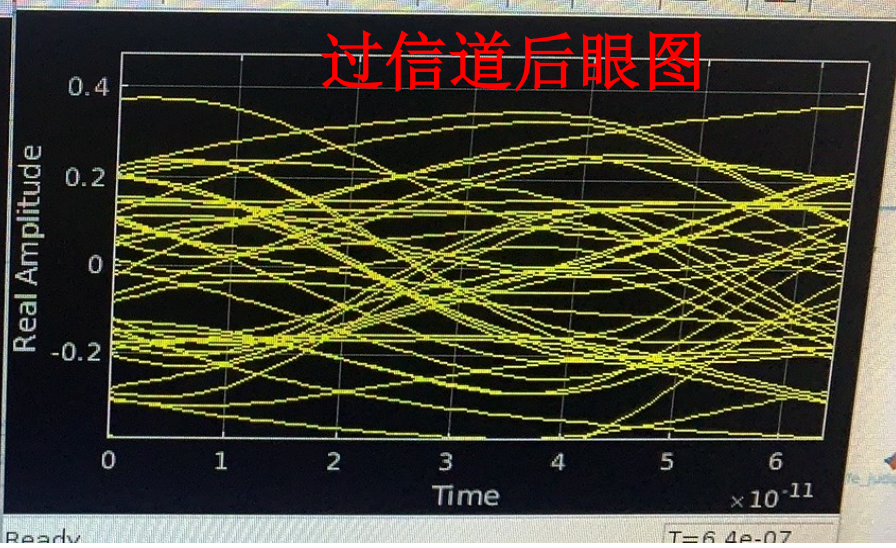
指标分频、模块开发  
、环路功能验证等



发送眼图

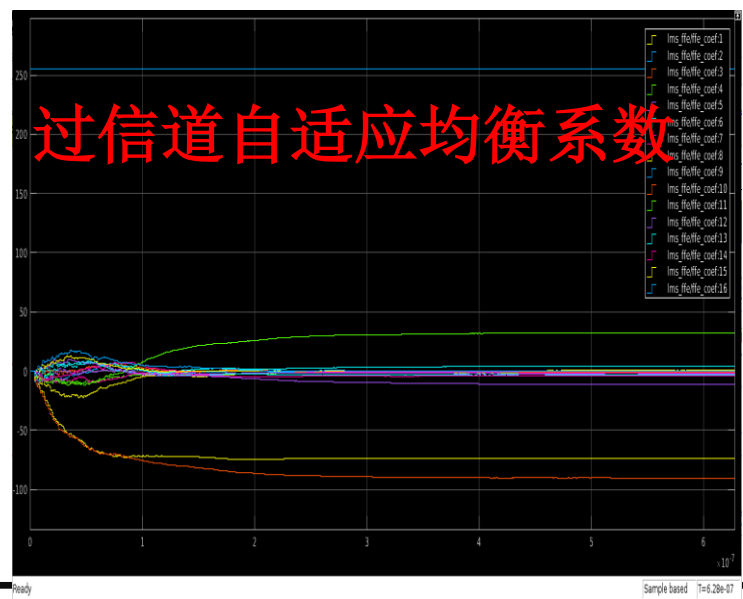


过信道后眼图

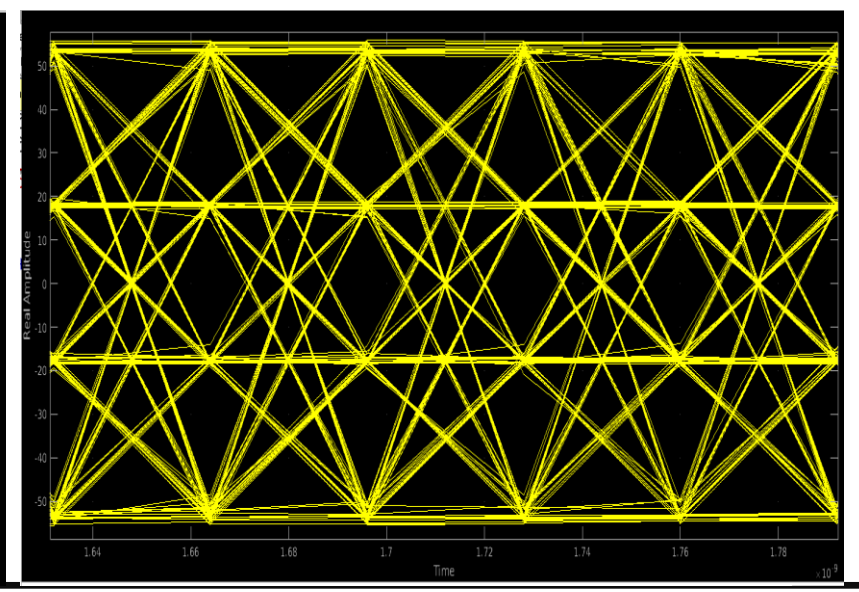
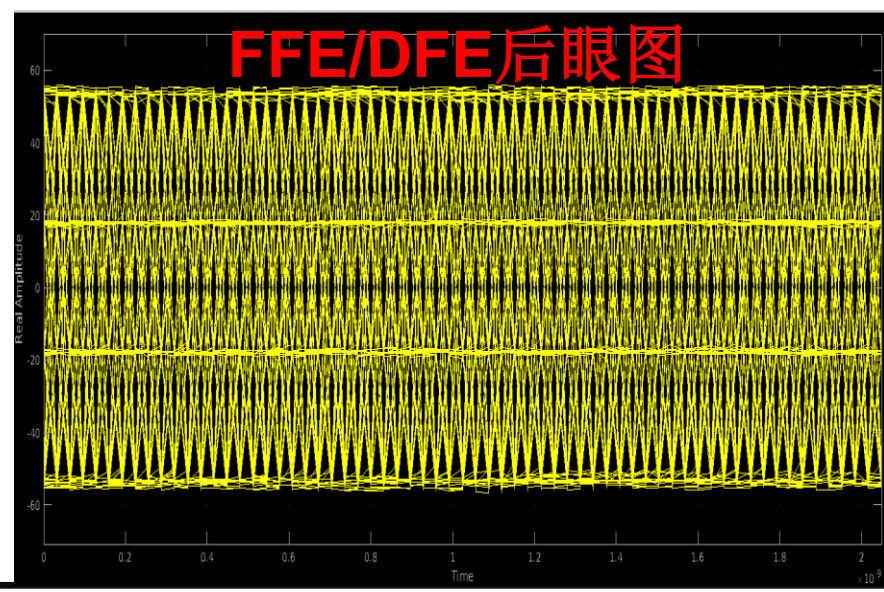


环路自适应  
算法级验证

过信道自适应均衡系数



FFE/DFE后眼图

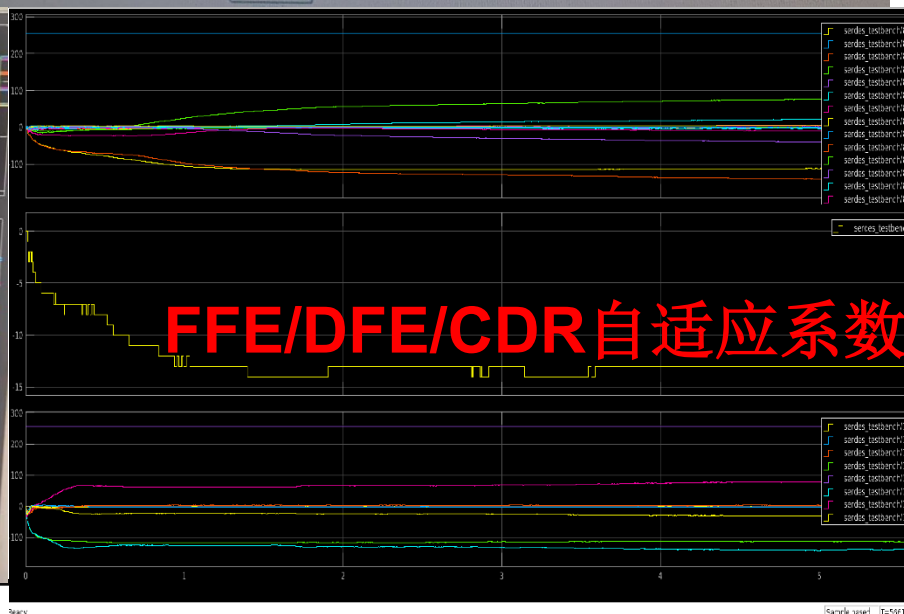
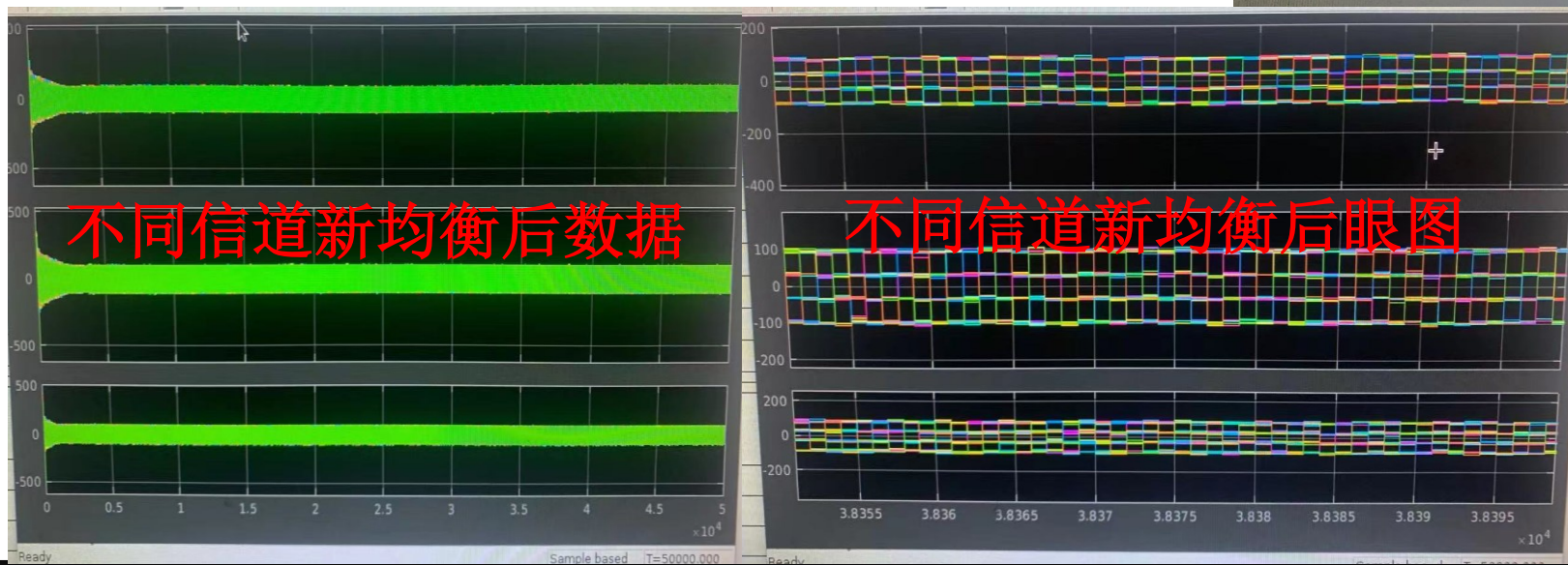
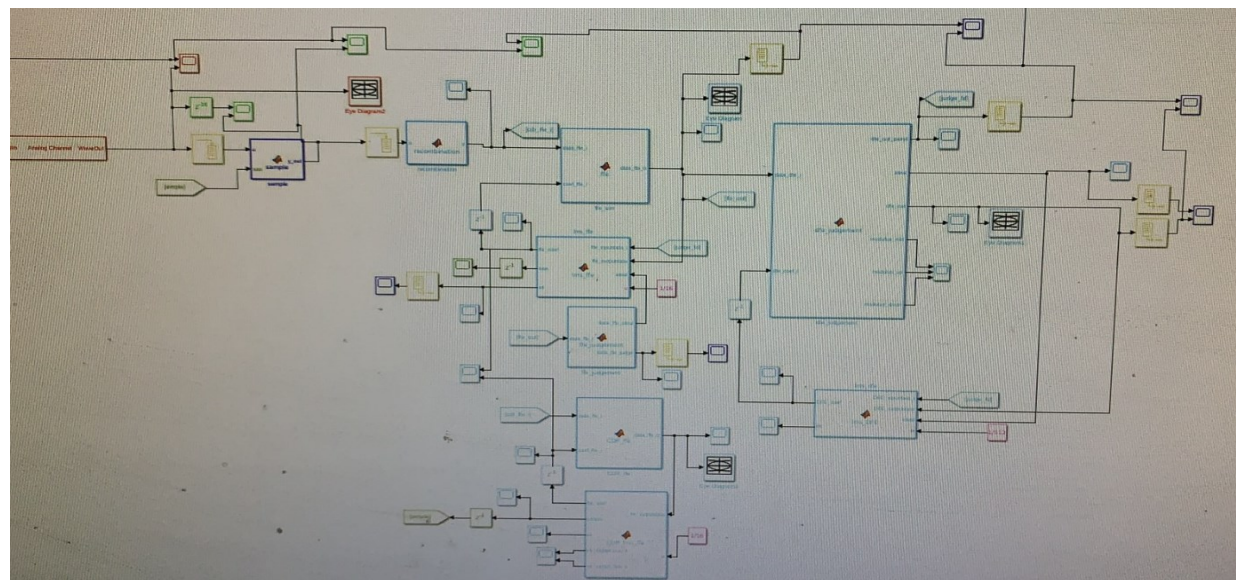




## 实现自适应环路的RTL级验证

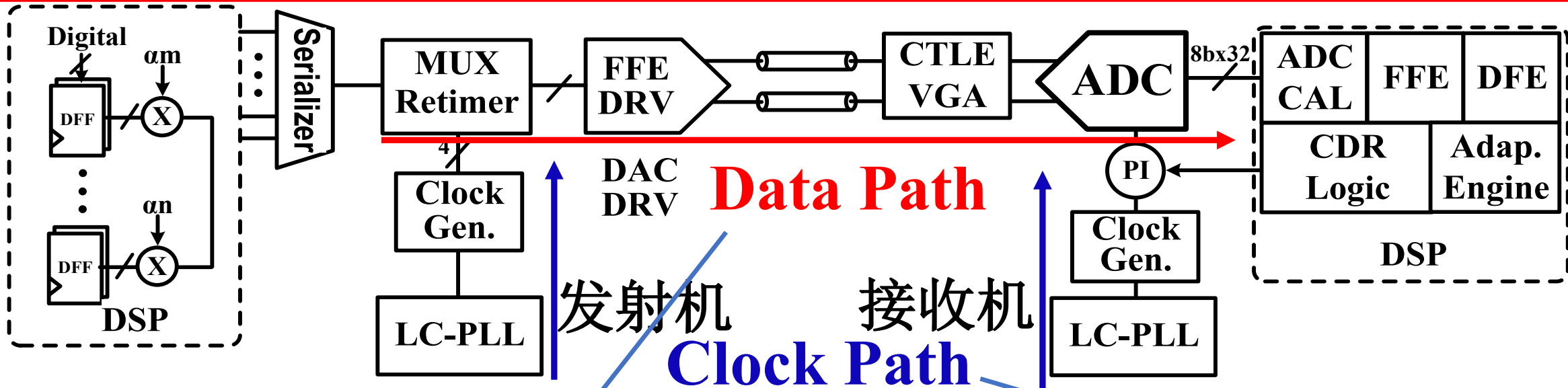
### DSP中RTL代替Matlab

- ◆ 引入实际时序
- ◆ 有限位精度取代浮点型精度



# ADC/DSP-Based LR SerDes - 主要技术特征

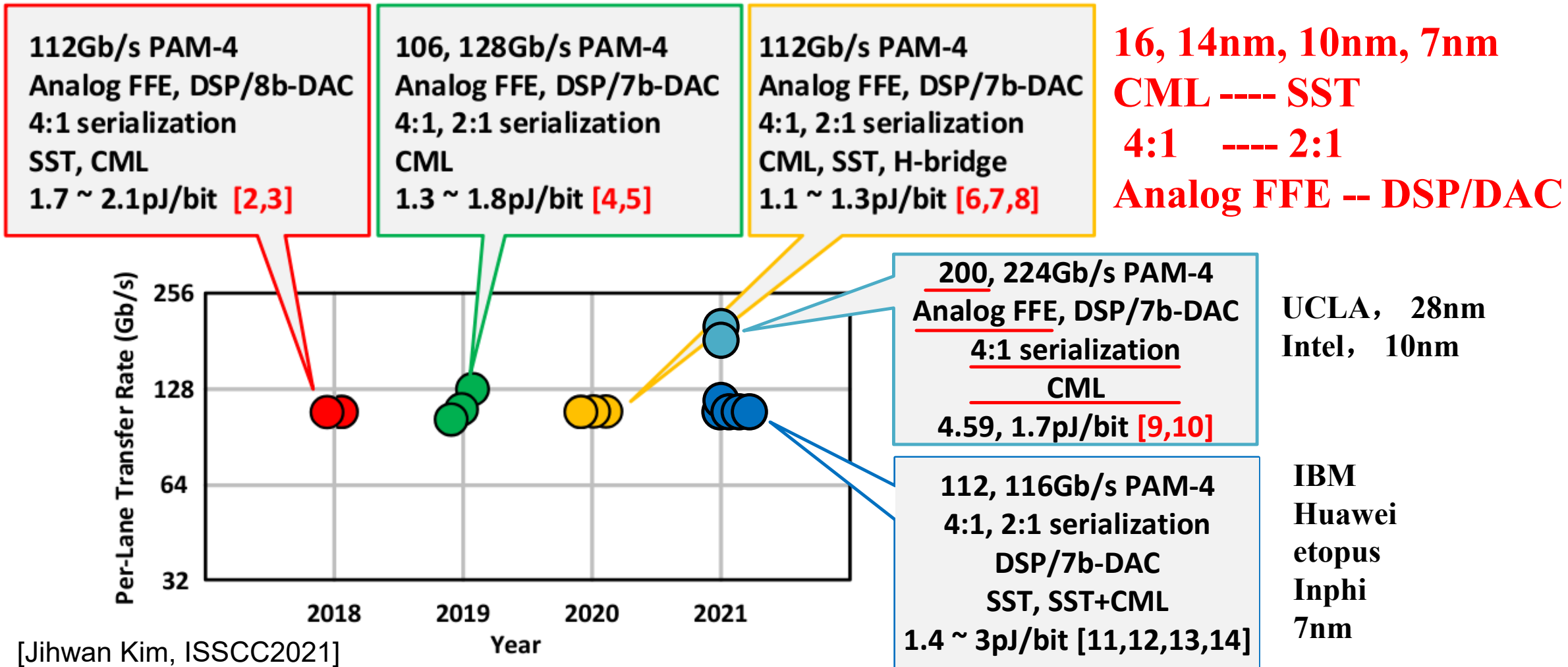
20/36



- ◆ Precise Timing
- ◆ High Bandwidth
- ◆ Large Swing
- ◆ High Linearity
- ◆ Adaptive Equalization

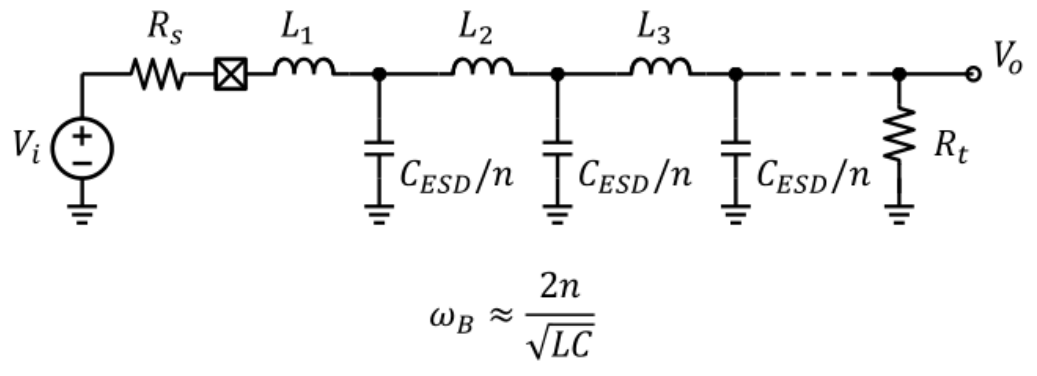
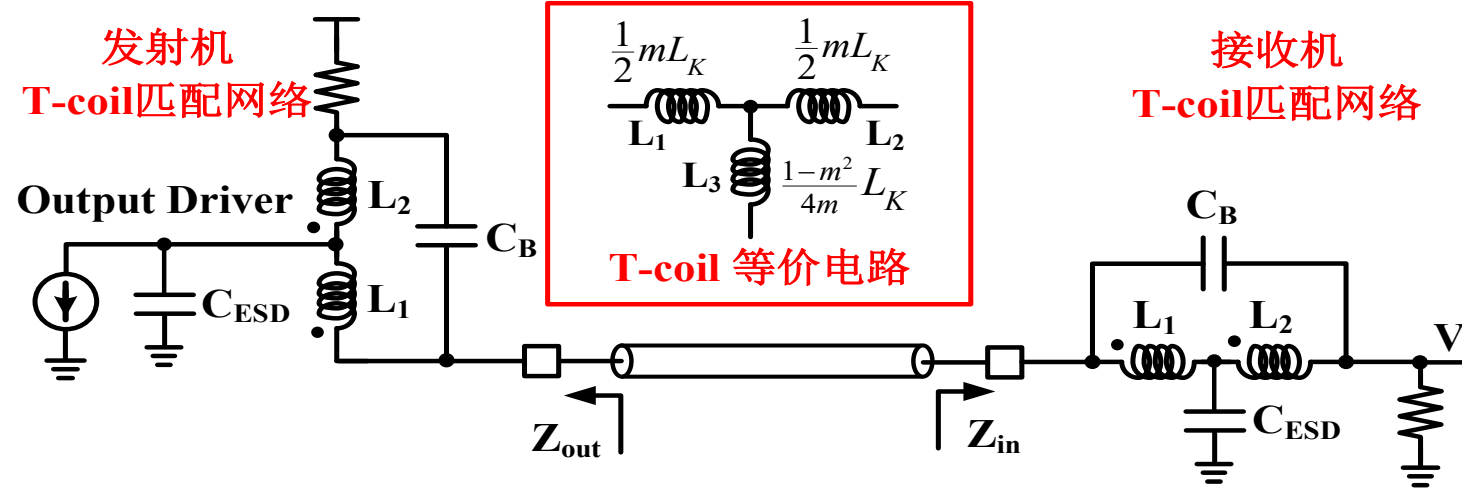
- ◆ Low Jitter
- ◆ Precise Phase
- ◆ Strong Tracking Ability





**Published in ISSCC in last four years**

# 数据通路-接收机-宽带匹配



Alphawave 200G PAM4, ISSCC2022

eTopus 56/112G, ISSCC2022

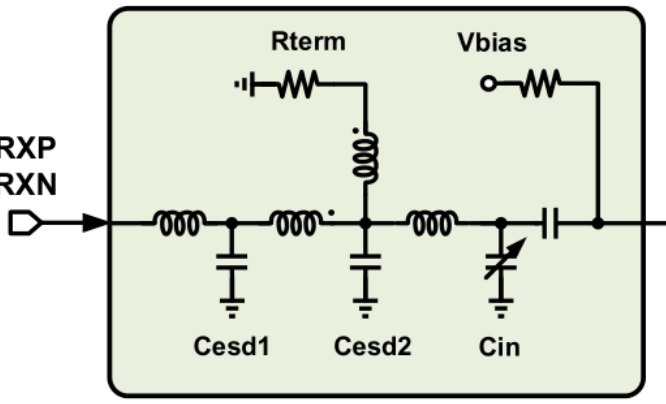
56/112G

Tcoil/Tcoil Variants

>200G

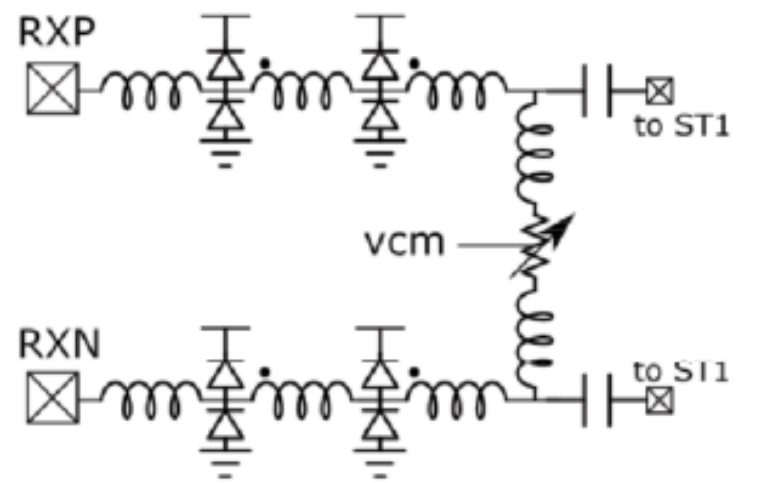
Artificial Transmission Line

Higher Speed

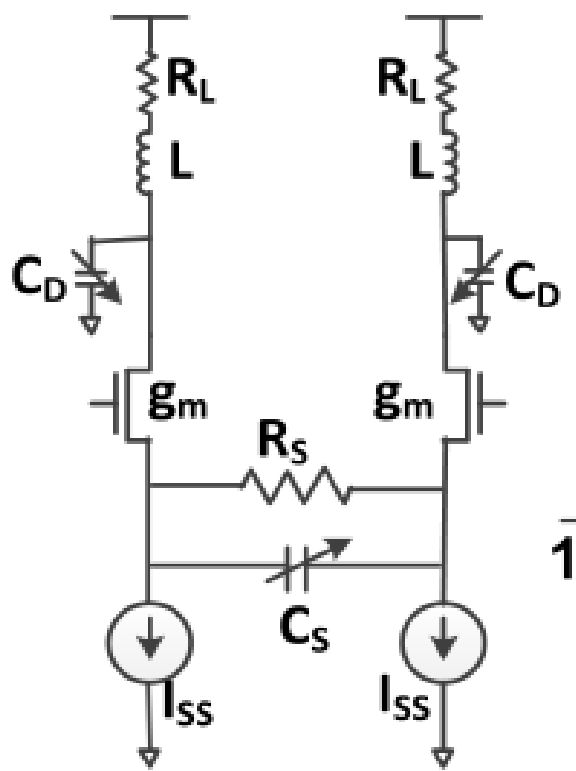


Marvell 112G, ISSCC2022

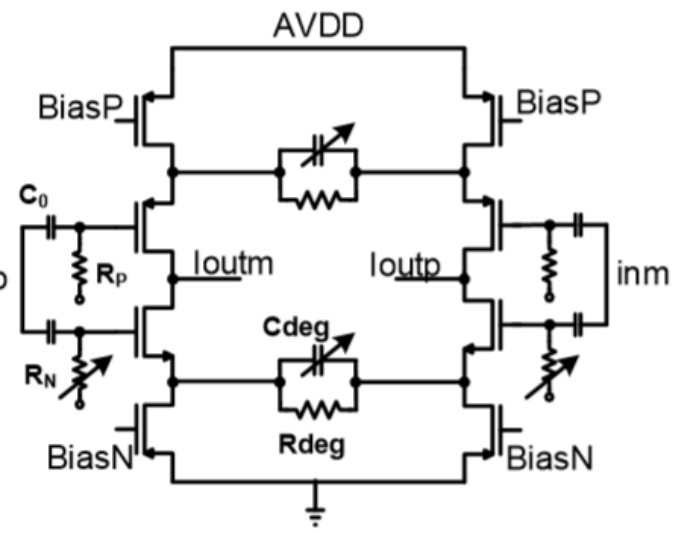
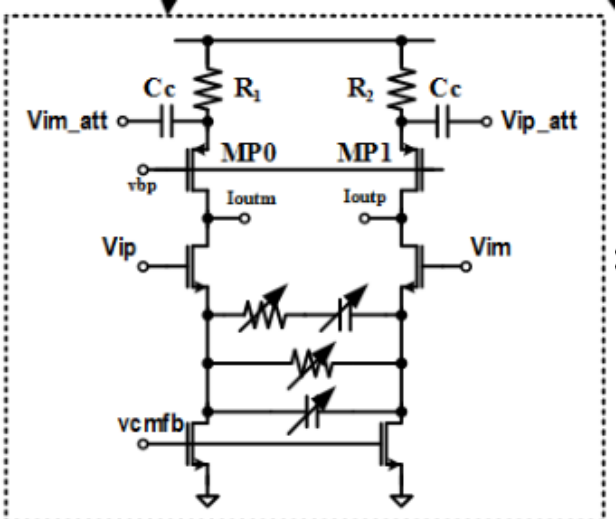
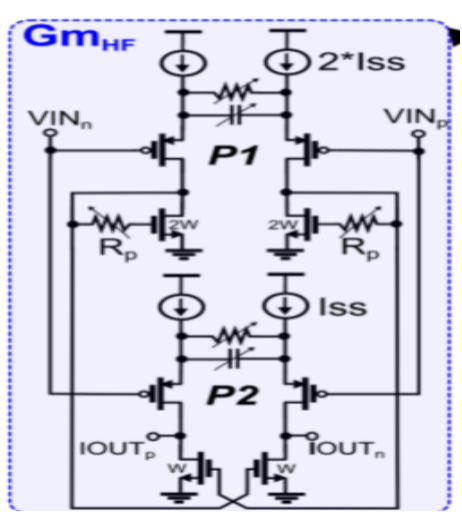
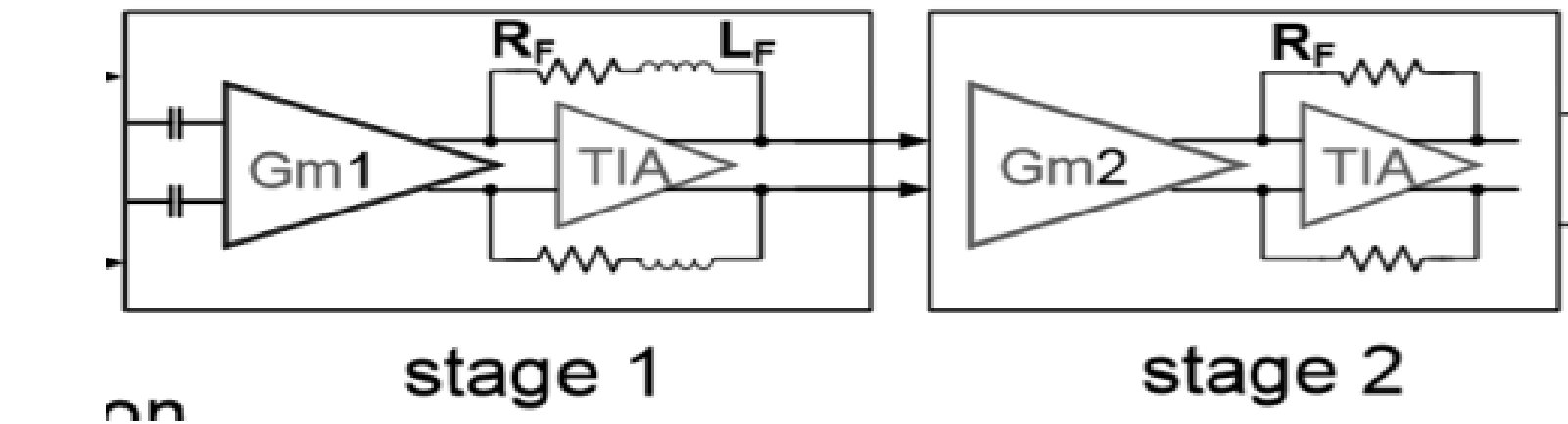
Inphi 112G, ISSCC2021



Intel 200G PAM4, ISSCC2022



Inductive peaking  
Source degeneration

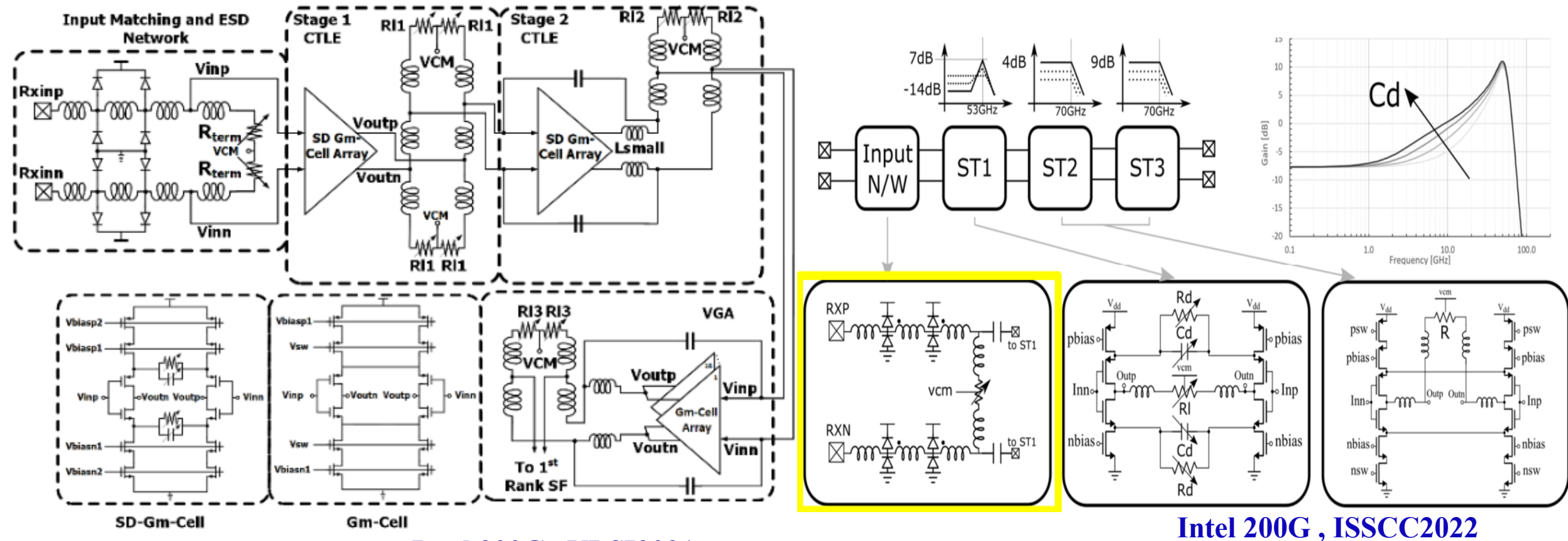


Gm-TIA Topology to Archive High Bandwidth

Xilinx 56G , JSSC2017  
Inphi 112G,ISSCC2021

IBM 112G , ISSCC2019    Huawei 112G , ISSCC2021    Marvel 112G , ISSCC2022

# 数据通路-接收机-CTLE

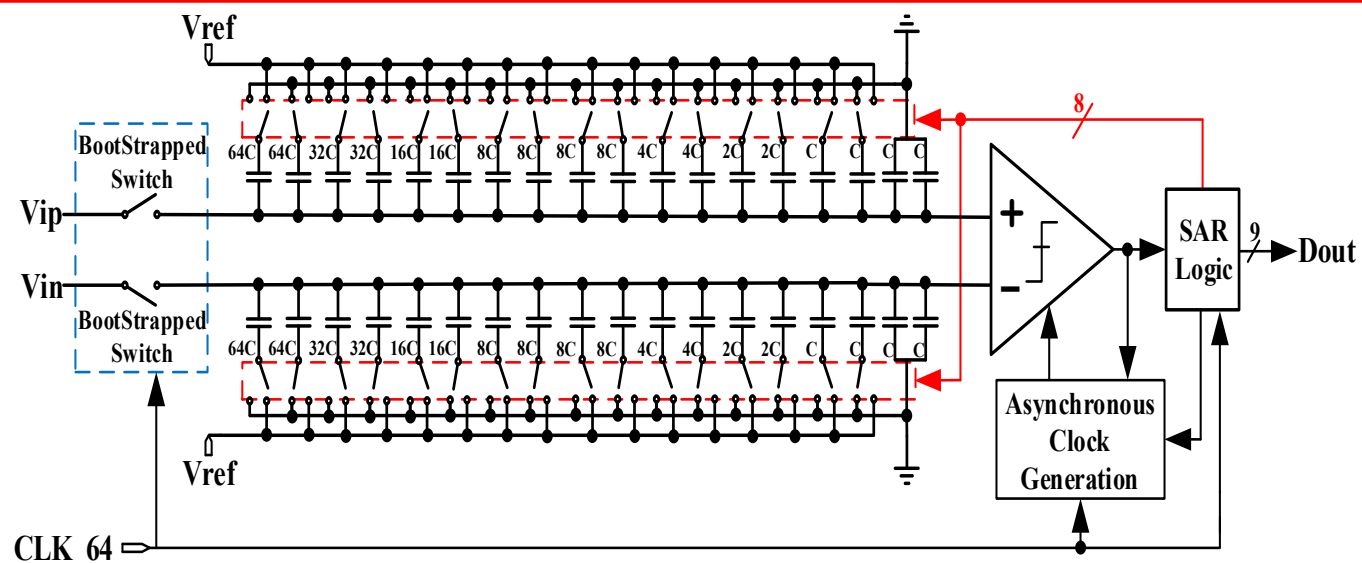
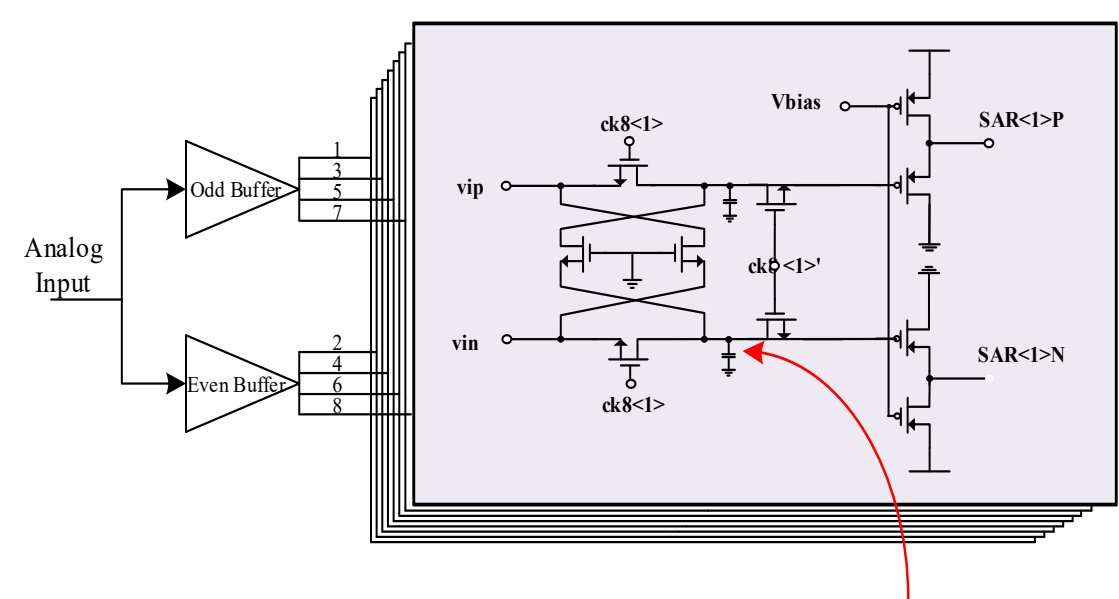


Intel 200G , VLSI2021

Intel 200G , ISSCC2022

Negative Miller C extend bandwidth (S1)  
 Small Ls extend bandwidth (S2)

CMOS driving architecture  
 Inductive peaking and source degeneration (CTLE)  
 Series-shunt inductive peaking (VGA)

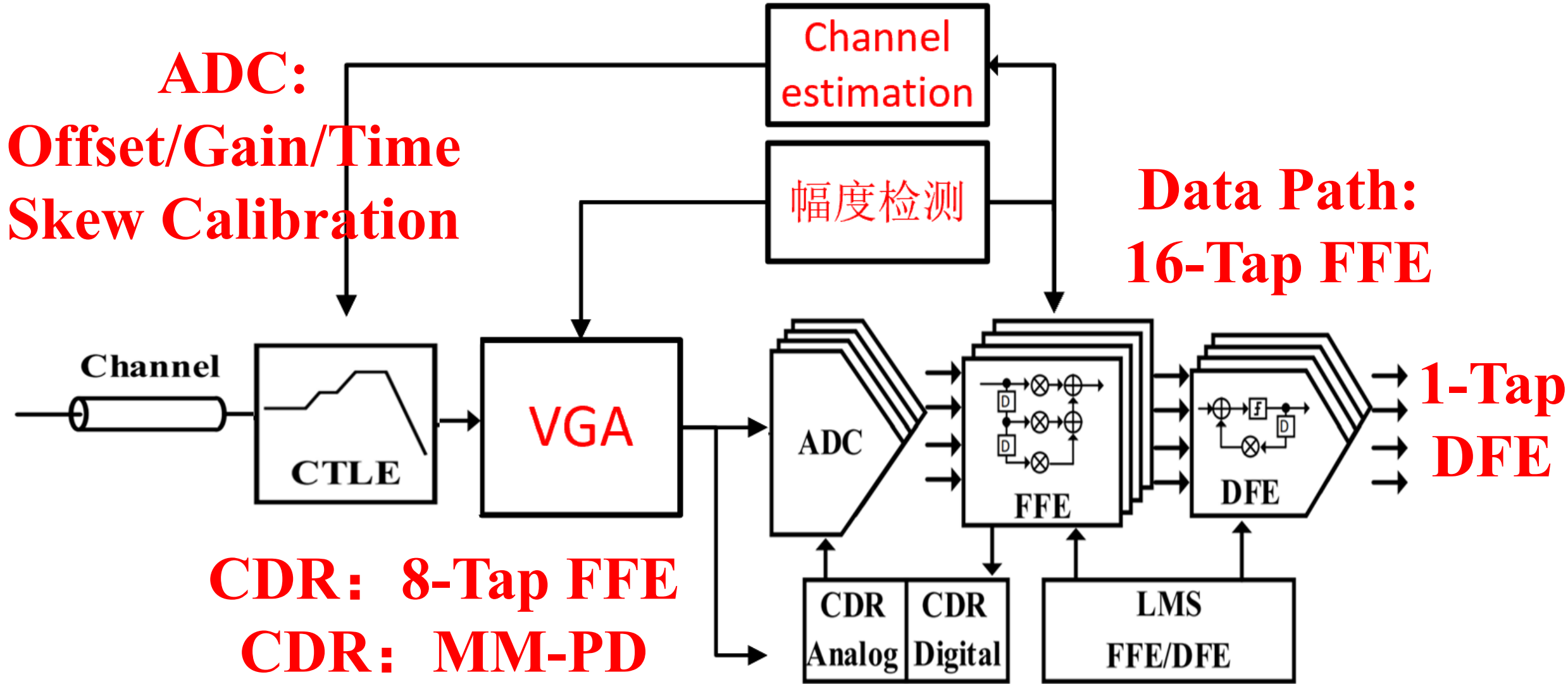


- ◆ 8X8 模拟前端，带宽超过25GHz，交织前端功耗100mW
- ◆ 顶板采样技术，Splitting & Monotonic的开关策略
- ◆ 采用Double-Tail比较器，动态失调校准电路
- ◆ 6-8bits模式调节

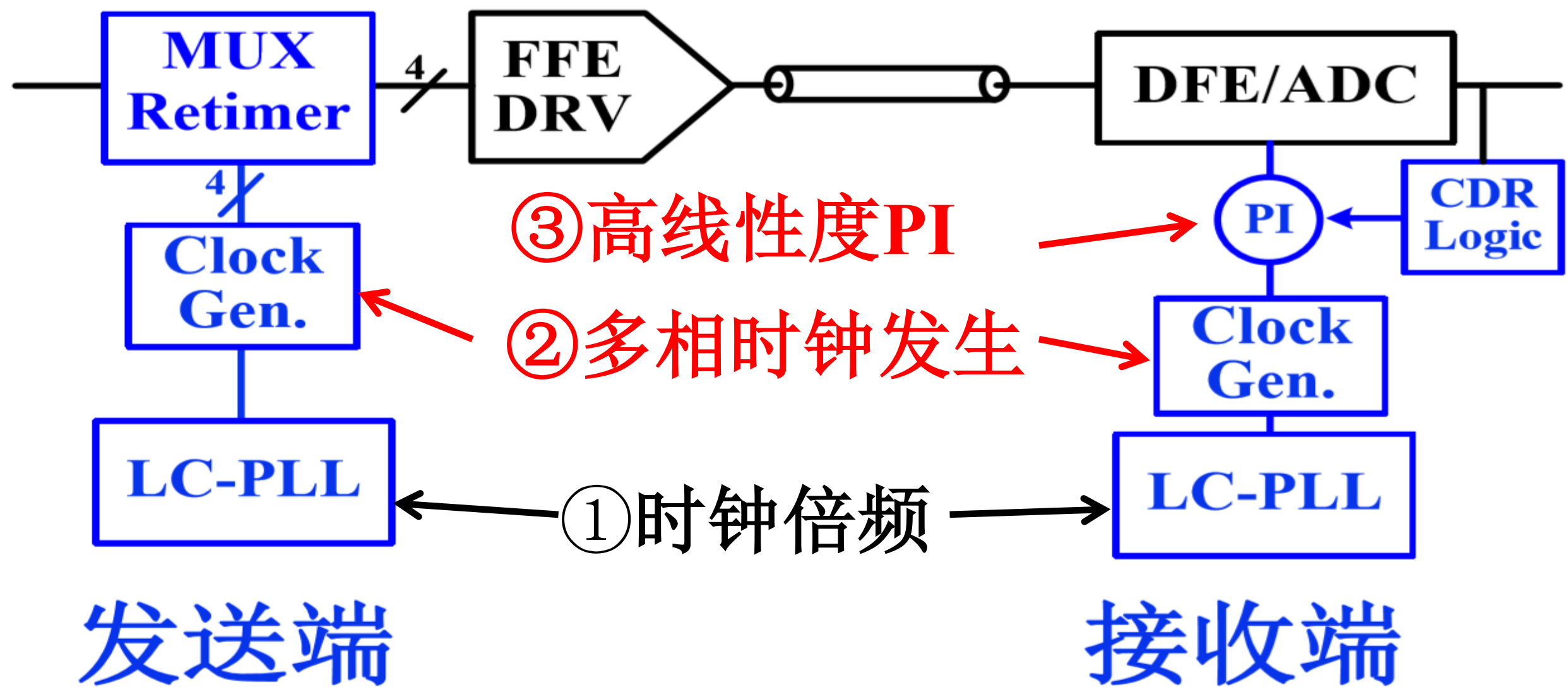
小面积  
小寄生  
小功耗

速度：1GS/s； 功耗：3.5mW； 摆幅：500mV； SFDR:>55dB； ENOB:>6.5

# 数据通路-接收机-DSP

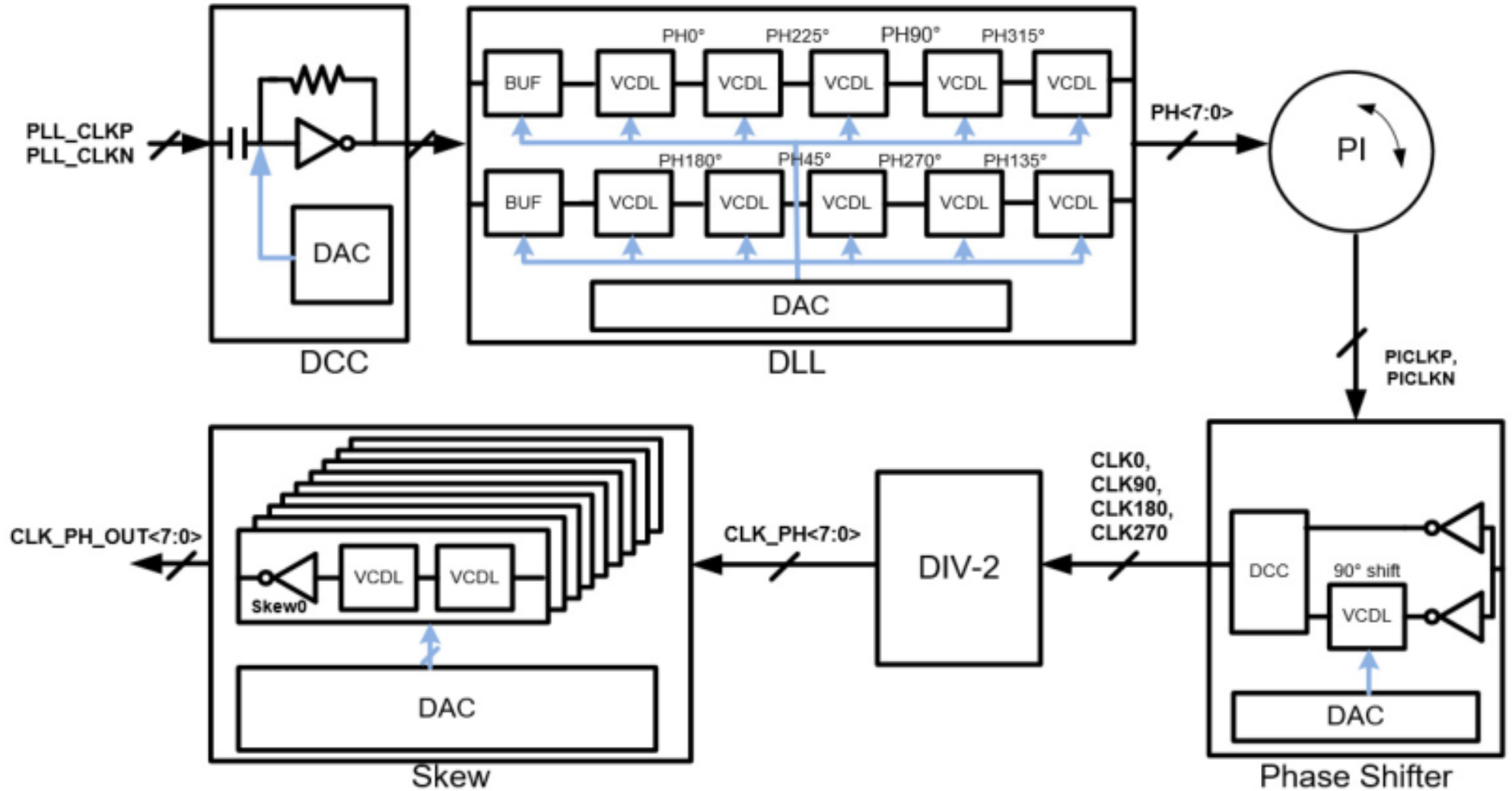






# 时钟通路-基于DLL的多相时钟产生

主要优势  
环路稳定



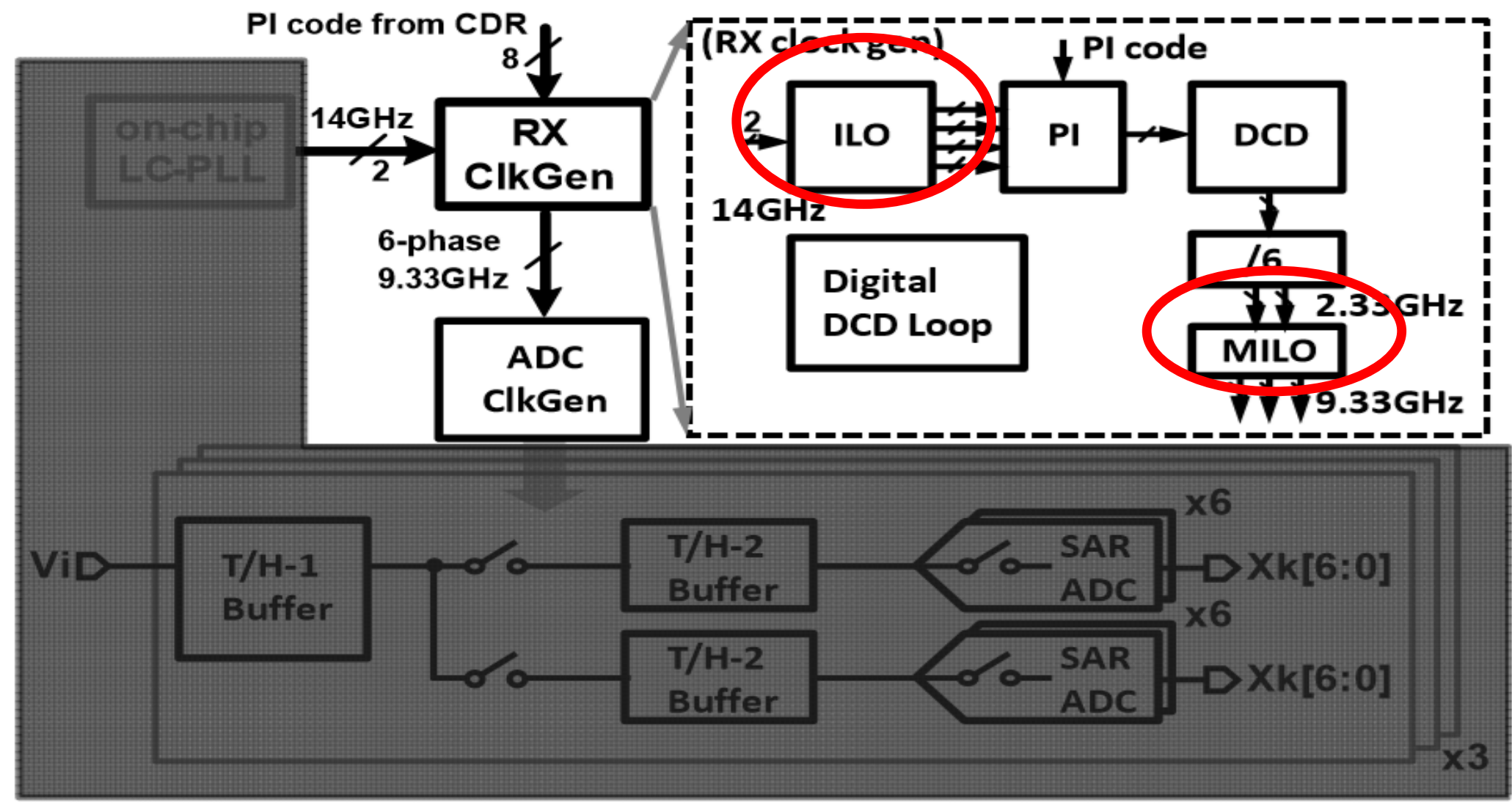
主要挑战  
DLL校准  
X2校准  
功耗

Marvel ISSCC2022

# 时钟通路-基于ILO的多相时钟产生

主要优势  
紧凑简洁  
低功耗

三个挑战  
频率追踪  
锁定范围  
相位拉拽



Xilinx ISSCC2020



- SerDes发展趋势与应用场景
- SerDes研究方法与关键技术
  - ◆ 系统级建模与仿真
  - ◆ 电路级技术演进
- 基于ADC/DSP PAM4 收发机

- ① **系统复杂、涉及模块多**: 基准、偏置、LDO、ADC、DAC、PLL、CDR、FFE/DFE、Adaptation Algrithom、Calibration
- ② **知识密集、涉及学科多**: 模集、数集、射频、微波、信号与系统、数字信号处理、matlab、systemverilog、EMX/HFSS
- ③ **协同要求高、涉及工种多**: 系统建模工程师、模拟电路工程师、射频微波工程师、模拟版图工程师、数字前端工程师、数字验证工程师、数字后端工程师、封装设计工程师、PCB设计工程师、测试工程师
- ④ **工艺要求高**: 产品团队的不能做, 培养团队的做不起。

Year of Production	2012	2015	2017	2019	2022	2025
CMOS node	40nm	28nm	16nm	7nm	3nm	2.1nm
Power, W/100G	50	20	7	2	1	0.5
Power efficiency, pJ/bit	500	200	70	20	10	5

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谢谢！  
欢迎交流

